





CC2652R7 JAJSM48B - MAY 2021 - REVISED MARCH 2023

# CC2652R7 SimpleLink™ マルチプロトコル 2.4GHz ワイヤレス MCU

# 1 特長

# ワイヤレス・マイコン

Texas

- 強力な 48MHz Arm® Cortex®-M4F プロセッサ
- 704KB フラッシュ・プログラム・メモリ
- プロトコルおよびライブラリ機能用の 256KB ROM
- 8KB のキャッシュ SRAM
- 高信頼性動作に適した 144KB の超低リーク SRAM (パリティ付き)
- ダイナミック・マルチプロトコル・マネージャ (DMM) ドラ イバ
- プログラマブルな無線機能には、2-(G)FSK、4-(G)FSK, MSK, Bluetooth® 5.2 Low Energy, IEEE 802.15.4 PHY、MAC のサポートが含まれます。
- OTA (Over-The-Air) アップグレードに対応

# 超低消費電力センサ・コントローラ

- 4KB の SRAM を備えた自律型 MCU
- センサ・データのサンプリング、保存、処理 •
- 高速ウェークアップによる低消費電力動作
- ソフトウェア定義ペリフェラル、静電容量式タッチ、流量 計、LCD

# 低い消費電力

- MCU の消費電流:
  - 3.10mA (アクティブ・モード、CoreMark)
  - 65µA/MHz (CoreMark 実行中)
  - 0.9µA (スタンバイ・モード、RTC、144KB RAM)
  - 0.1µA (シャットダウン・モード、ウェイクアップ・オン・ ピン)
- 超低消費電力センサ・コントローラの消費電流:
  - 29.2µA (2MHz モード)
  - 799µA (24MHz モード)
- 無線の消費電流:
  - 6.4mA (RX)
  - 7.3mA (TX, 0dBm)
  - 9.7mA (TX, +5dBm)

### 無線プロトコルのサポート

- Thread, Zigbee®, Matter
- ٠ Bluetooth® 5.2 Low Energy
- SimpleLink™ TI 15.4 スタック
- 6LoWPAN
- 独自システム

# 高性能の無線

- -104dBm (Bluetooth® Low Energy, 125kbps)
- 温度補償付きで最大 +5dBm の出力電力

# 法規制の順守

- 以下の規格への準拠を目的としたシステムに最適:
- ETSI EN 300 328、EN 300 440 Cat.2 および 3
- FCC CFR47 Part 15
- ARIB STD-T66

## マイコンのペリフェラル

- デジタル・ペリフェラルを任意の GPIO に接続可能
- 4 つの 32 ビットまたは 8 つの 16 ビット汎用タイマ
- 12 ビット ADC、200k サンプル/秒、8 チャネル
- 8ビット DAC
- 2 つのコンパレータ
- プログラマブルな電流ソース
- 2 つの UART、2 つの SSI、I<sup>2</sup>C、I<sup>2</sup>S
- リアルタイム・クロック (RTC)
- 温度およびバッテリ・モニタを内蔵

# セキュリティを実現する機能

- AES 128 および 256 ビット暗号化アクセラレータ
- ECC および RSA 公開鍵ハードウェア・アクセラレータ
- SHA2 アクセラレータ (SHA-512 までのフル・スイート)
- 真性乱数生成器 (TRNG)

# 開発ツールとソフトウェア

- LP-CC2652R7 開発キット
- SimpleLink™ CC13xx/CC26xx ソフトウェア開発キッ ト (SDK)
- SmartRF<sup>™</sup> Studio による容易な無線構成
- Sensor Controller Studio により低消費電力のセンシ ング・アプリケーションを構築
- SysConfig システム・コンフィギュレーション・ツール

# 動作範囲

- オンチップの降圧型 DC/DC コンバータ
- 1.8V~3.8V のシングル電源電圧
- 1.7V~1.95V の外部レギュレータ・モード
- -40~+105°C

# パッケージ

- 7mm × 7mm RGZ VQFN48 (31GPIO)
- RoHS 準拠のパッケージ



INSTRUMENTS



# 2 アプリケーション

- 2400~2500MHzのISM および SRD システム<sup>1</sup> (最小 4kHzの受信帯域幅)
- ビル・オートメーション
  - ビル・セキュリティ・システム モーション検出器、電子スマート・ロック、ドアおよび窓センサ、ガレージ・ ドア・システム、ゲートウェイ
  - HVAC サーモスタット、ワイヤレス環境センサ、
     HVAC システム・コントローラ、ゲートウェイ
  - 防火システム 煙および熱感知器、火災警報制御 パネル (FACP)
  - ビデオ監視 IP ネットワーク・カメラ
  - エレベータとエスカレータ エレベータおよびエス カレータのためのエレベータ・メイン制御パネル

- ・ 産業用輸送 アセット・トラッキング
- ファクトリ・オートメーション / 制御
- 医療用
- 電子 POS (EPOS) 電子棚札 (ESL)
- 通信機器
  - 有線ネットワーク 無線 LAN または Wi-Fi アクセス・ポイント、エッジ・ルータ、小規模企業向けルータ
- パーソナル・エレクトロニクス
  - ホーム・シアター/エンターテインメント-スマート・ スピーカ、スマート・ディスプレイ、セット・トップ・ボッ クス
  - ウェアラブル (医療以外) スマート・トラッカー、ス マート衣料

# 3 概要

SimpleLink<sup>™</sup> CC2652R7 デバイスはマルチプロトコル 2.4GHz ワイヤレス・マイクロコントローラ (MCU) です。本デバイスは Thread、Zigbee<sup>®</sup>、Matter、Bluetooth<sup>®</sup> 5.2 Low Energy、IEEE 802.15.4g、IPv6 対応スマート・オブジェクト (6LoWPAN)、TI 15.4 スタック (2.4GHz)、DMM (ダイナミック・マルチプロトコル・マネージャ)ドライバを使った同時マル チプロトコルをサポートしています。CC2652R7 は、Arm<sup>®</sup> Cortex<sup>®</sup> M4F メイン・プロセッサを基に設計されており、グリッド・インフラストラクチャ、ビル・オートメーション、リテール・オートメーション、パーソナル・エレクトロニクス、医療用アプリケーションの低消費電力の無線通信と先進センシングに最適化されています。

CC2652R7 は、Arm® Cortex® M0 で実行するソフトウェア無線を内蔵しているため、各種の物理層とRF 規格をサポートできます。本デバイスは、2360~2500MHz の周波数帯域での動作をサポートしています。PHY と周波数の切り換えは、DMM (ダイナミック・マルチプロトコル・マネージャ)ドライバを使って実行時に行うことができます。CC2652R7 は、2.4GHz 帯で +5dBm TX (9.7mA) をサポートしています。CC2652R7 は -104dBm (125kbps の Bluetooth® Low Energy Coded PHY) の受信感度を実現しています。

CC2652R7 は 0.9µA の低スリープ電流 (RTC 動作、144KB RAM を保持) を実現しています。メインの Cortex® M4F プロセッサに加えて、高速ウェイクアップ機能を備えた自律型超低消費電力センサ・コントローラ CPU も内蔵しています。 たとえば、このセンサ・コントローラは、1µA のシステム電流で 1Hz の ADC サンプリングが可能です。

CC2652R7 は、動作寿命を伸ばすために低 SER (ソフト・エラー・レート) FIT (Failure-in-time) を実現しています。常時 オンの SRAM パリティにより、潜在的な放射線イベントによる破損のリスクを最小限に抑えています。多くのお客様の 10 ~15 年またはそれ以上の長いライフ・サイクル要件に沿って、TI は、製品寿命と製品供給の継続性を約束する製品ライ フ・サイクル・ポリシーを制定しています。

CC2652R7 デバイスは SimpleLink<sup>™</sup> MCU プラットフォームの一部です。このプラットフォームは Wi-Fi®、*Bluetooth*® Low Energy、Thread、Zigbee、Wi-SUN®、Amazon Sidewalk、mioty®、Sub-1GHz MCU、ホスト MCU で構成されま す。CC2652R7 は、32KB~704KB のフラッシュ・サイズに対応し、ピン互換パッケージを選択可能なスケーラブルなポ ートフォリオの一部です。共通の SimpleLink<sup>™</sup> CC13xx および CC26xx ソフトウェア開発キット (SDK) と SysConfig シ ステム・コンフィギュレーション・ツールはポートフォリオ内のデバイス間の移行を支援します。多数のソフトウェア・スタック、 アプリケーション例、SimpleLink<sup>™</sup> Academy トレーニング・セッションが本 SDK に含まれます。詳細については、ワイヤ レス・コネクティビティ製品をご覧ください。

<sup>&</sup>lt;sup>1</sup> サポートしているプロトコル規格、変調フォーマット、データ・レートの詳細については、RF コアを参照してください。



	製品情報		
部品番号 <sup>(1)</sup> パッケージ     本体サイズ (公			
CC2652R74T0RGZR	VQFN (48)	7.00mm × 7.00mm	

(1) 提供中の全デバイスに関する最新の製品、パッケージ、および注文情報についてはセクション 11 のパッケージ・オプションについての付録、また は TI Web サイトを参照してください。

# 3.1 機能ブロック図

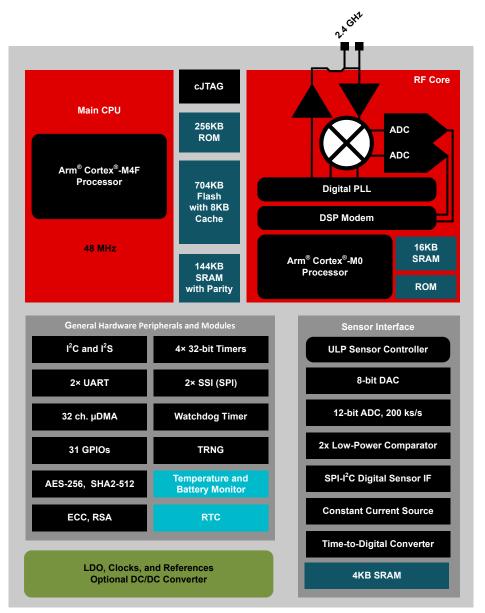


図 3-1. CC2652R7 ブロック図



# **Table of Contents**

1	特長1
2	アプリケーション2
3	概要2
	3.1 機能ブロック図3
4	Revision History4
5	Device Comparison5
6	Terminal Configuration and Functions
	6.1 Pin Diagram – RGZ Package (Top View)6
	6.2 Signal Descriptions – RGZ Package7
	6.3 Connections for Unused Pins and Modules8
7	Specifications
	7.1 Absolute Maximum Ratings9
	7.2 ESD Ratings
	7.3 Recommended Operating Conditions9
	7.4 Power Supply and Modules
	7.5 Power Consumption - Power Modes
	7.6 Power Consumption - Radio Modes
	7.7 Nonvolatile (Flash) Memory Characteristics
	7.8 Thermal Resistance Characteristics
	7.9 RF Frequency Bands
	7.10 Bluetooth Low Energy - Receive (RX)
	7.11 Bluetooth Low Energy - Transmit (TX)
	7.12 Zigbee and Thread - IEEE 802.15.4-2006 2.4
	GHz (OQPSK DSSS1:8, 250 kbps) - RX
	GHz (OQPSK DSSS1:8, 250 kbps) - TX
	7.14 Timing and Switching Characteristics
	7.15 Peripheral Characteristics
	7.16 Typical Characteristics

8 Detailed Description	35
8.1 Overview	35
8.2 System CPU	35
8.3 Radio (RF Core)	
8.4 Memory	
8.5 Sensor Controller	37
8.6 Cryptography	38
8.7 Timers	39
8.8 Serial Peripherals and I/O	40
8.9 Battery and Temperature Monitor	
8.10 µDMA	
8.11 Debug	40
8.12 Power Management	41
8.13 Clock Systems	42
8.14 Network Processor	42
9 Application, Implementation, and Layout	
9.1 Reference Designs	43
9.2 Junction Temperature Calculation	43
10 Device and Documentation Support	
10.1 Device Nomenclature	45
10.2 Tools and Software	45
10.3 Documentation Support	<mark>48</mark>
10.4 サポート・リソース	48
10.5 Trademarks	48
10.6 静電気放電に関する注意事項	49
10.7 用語集	
11 Mechanical, Packaging, and Orderable	
Information	50

# **4 Revision History**

資料番号末尾の英字は改訂を表しています。その改訂履歴は英語版に準じています。

# Changes from November 30, 2021 to March 10, 2023 (from Revision A (November 2021) to Revision B (March 2023))

R	evision B (March 2023))	Page
•	セクション1の動作範囲に外部レギュレータ・モードを追加	1
•	Added External Regulator Mode to セクション 6.2	7
•	Added External Regulator Mode to セクション 6.3	8
•	Added External Regulator Mode added to セクション 7.1, セクション 7.3, and セクション 7.4	9



# **5 Device Comparison**

DEVICE RADIO SUPPORT		FLASH (KB)	RAM (KB)	GPIO	PACKAGE SIZE
CC1310	Sub-1 GHz Wireless M-Bus	32-128	16-20	10-30	RGZ (7-mm × 7-mm VQFN48) RHB (5 mm × 5 mm VQFN32) RSM (4 mm × 4 mm VQFN32)
CC1312R	CC1312R Sub-1 GHz Wi-SUN® Amazon Sidewalk Wireless M-Bus Multiprotocol Sub-1 GHz Wi-SUN® Amazon Sidewalk Wireless M-Bus Bluetooth 5.2 Low Energy Zigbee Thread 2.4 GHz proprietary FSK-based formats +20-dBm high-power amplifier		80-144	30	RGZ (7-mm × 7-mm VQFN48)
CC1352P			80-144	26	RGZ (7-mm × 7-mm VQFN48)
CC1352R	Multiprotocol Sub-1 GHz Wi-SUN® Wireless M-Bus Bluetooth 5.2 Low Energy Zigbee Thread 2.4 GHz proprietary FSK-based formats	352	80	28	RGZ (7-mm × 7-mm VQFN48)
CC2642R	Bluetooth 5.2 Low Energy 2.4 GHz proprietary FSK-based formats	352	80	31	RGZ (7-mm × 7-mm VQFN48)
CC2642R-Q1	Bluetooth 5.2 Low Energy	352	80	31	RTC (7-mm × 7-mm VQFN48)
CC2652R	Multiprotocol Bluetooth 5.2 Low Energy Zigbee Thread 2.4 GHz proprietary FSK-based formats	352-704	80-144	31	RGZ (7-mm × 7-mm VQFN48)
CC2652RB	Multiprotocol Bluetooth 5.2 Low Energy Zigbee Thread	352	80	31	RGZ (7-mm × 7-mm VQFN48)
CC2652P	Multiprotocol Bluetooth 5.2 Low Energy Zigbee Thread 2.4 GHz proprietary FSK-based formats +19.5-dBm high-power amplifier	352-704	80-144	26	RGZ (7-mm × 7-mm VQFN48)

# 表 5-1. Device Family Overview



# **6** Terminal Configuration and Functions

# 6.1 Pin Diagram – RGZ Package (Top View)

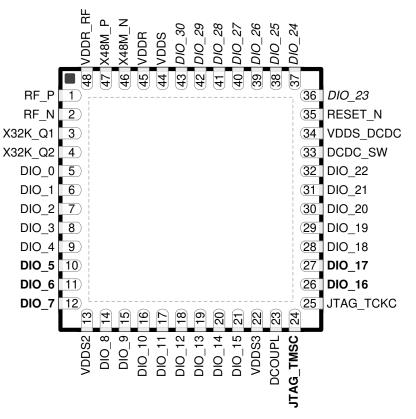


図 6-1. RGZ (7-mm × 7-mm) Pinout, 0.5-mm Pitch (Top View)

The following I/O pins marked in 🗵 6-1 in **bold** have high-drive capabilities:

- Pin 10, DIO\_5
- Pin 11, DIO\_6
- Pin 12, DIO\_7
- Pin 24, JTAG\_TMSC
- Pin 26, DIO\_16
- Pin 27, DIO\_17

The following I/O pins marked in  $\boxtimes$  6-1 in *italics* have analog capabilities:

- Pin 36, DIO\_23
- Pin 37, DIO\_24
- Pin 38, DIO\_25
- Pin 39, DIO\_26
- Pin 40, DIO\_27
- Pin 41, DIO\_28
- Pin 42, DIO\_29
- Pin 43, DIO\_30



# 6.2 Signal Descriptions – RGZ Package

PIN TVPF PEOPIPTION				DECODIDION
NAME	NO.	I/O	TYPE	DESCRIPTION
DCDC_SW	33	—	Power	Output from internal DC/DC converter. Tie to ground for external regulator model (1.7-V to 1.95-V operation). <sup>(1)</sup>
DCOUPL	23	—	Power	For decoupling of internal 1.27-V regulated digital supply <sup>(2)</sup>
DIO_0	5	I/O	Digital	GPIO
DIO_1	6	I/O	Digital	GPIO
DIO_2	7	I/O	Digital	GPIO
DIO_3	8	I/O	Digital	GPIO
DIO_4	9	I/O	Digital	GPIO
DIO_5	10	I/O	Digital	GPIO, high-drive capability
DIO_6	11	I/O	Digital	GPIO, high-drive capability
DIO_7	12	I/O	Digital	GPIO, high-drive capability
DIO_8	14	I/O	Digital	GPIO
DIO_9	15	I/O	Digital	GPIO
DIO_10	16	I/O	Digital	GPIO
DIO_11	17	I/O	Digital	GPIO
DIO_12	18	I/O	Digital	GPIO
DIO_13	19	I/O	Digital	GPIO
DIO_14	20	I/O	Digital	GPIO
DIO_15	21	I/O	Digital	GPIO
DIO_16	26	I/O	Digital	GPIO, JTAG_TDO, high-drive capability
DIO_17	27	I/O	Digital	GPIO, JTAG_TDI, high-drive capability
DIO_18	28	I/O	Digital	GPIO
DIO_19	29	I/O	Digital	GPIO
DIO_20	30	I/O	Digital	GPIO
DIO_21	31	I/O	Digital	GPIO
 DIO_22	32	I/O	Digital	GPIO
 DIO_23	36	I/O	Digital or Analog	GPIO, analog capability
 DIO_24	37	I/O	Digital or Analog	GPIO, analog capability
 DIO_25	38	I/O	Digital or Analog	GPIO, analog capability
DIO_26	39	I/O	Digital or Analog	GPIO, analog capability
 DIO_27	40	I/O	Digital or Analog	GPIO, analog capability
 DIO_28	41	I/O	Digital or Analog	GPIO, analog capability
 DIO_29	42	I/O	Digital or Analog	GPIO, analog capability
 DIO_30	43	I/O	Digital or Analog	GPIO, analog capability
EGP			GND	Ground – exposed ground pad <sup>(3)</sup>
JTAG_TMSC	24	I/O	Digital	JTAG TMSC, high-drive capability
JTAG_TCKC	25	I	Digital	JTAG TCKC
RESET_N	35	I	Digital	Reset, active low. No internal pullup resistor
RF_P	1	_	RF	Positive RF input signal to LNA during RX Positive RF output signal from PA during TX
RF_N	2	_	RF	Negative RF input signal to LNA during RX Negative RF output signal from PA during TX

# 表 6-1. Signal Descriptions – RGZ Package



#### 表 6-1. Signal Descriptions – RGZ Package (continued)

PIN		1/0	ТҮРЕ	DESCRIPTION	
NAME	NO.	1/0	TIPE	DESCRIPTION	
VDDR	45	_	Power	Internal supply, must be powered from the internal DC/DC converter or the internal LDO. For external regulator mode (1.7-V to 1.95-V operation, connect to external regulator and internal DC-DC cannot be used. <sup>(2) (4) (6)</sup>	
VDDR_RF	48	_	Power	Internal supply, must be powered from the internal DC/DC converter or the internal LDO. For external regulator mode (1.7-V to 1.95-V operation, connect to external regulator and internal DC-DC cannot be used. <sup>(2) (5) (6)</sup>	
VDDS	44	_	Power	1.8-V to 3.8-V main chip supply. For external regulator mode (1.7-V to 1.95-V operation, connect to external regulator and internal DC-DC cannot be used. $^{(1)}$	
VDDS2	13	_	Power	1.8-V to 3.8-V DIO supply. For external regulator mode (1.7-V to 1.95-V operation, connect to external regulator and internal DC-DC cannot be used. <sup>(1)</sup>	
VDDS3	22	_	Power	1.8-V to 3.8-V DIO supply. For external regulator mode (1.7-V to 1.95-V operation, connect to external regulator and internal DC-DC cannot be used. <sup>(1)</sup>	
VDDS_DCDC	34	_	Power	1.8-V to 3.8-V DC/DC converter supply. Tie to ground for external regulator mode (1.7-V to 1.95-V operation).	
X48M_N	46		Analog	48-MHz crystal oscillator pin 1	
X48M_P	47		Analog	48-MHz crystal oscillator pin 2	
X32K_Q1	3		Analog	32-kHz crystal oscillator pin 1	
X32K_Q2	4	—	Analog	32-kHz crystal oscillator pin 2	

(1) For more details, see technical reference manual listed in セクション 10.3.

(2) Do not supply external circuitry from this pin.

(3) EGP is the only ground connection for the device. Good electrical connection to device ground on printed circuit board (PCB) is imperative for proper device operation.

(4) If internal DC/DC converter is not used, this pin is supplied internally from the main LDO.

(5) If internal DC/DC converter is not used, this pin must be connected to VDDR for supply from the main LDO.

(6) Output from internal DC/DC and LDO is trimmed to 1.68 V.

# 6.3 Connections for Unused Pins and Modules

#### 表 6-2. Connections for Unused Pins - RGZ Package

FUNCTION	SIGNAL NAME	PIN NUMBER	ACCEPTABLE PRACTICE <sup>(1)</sup>	PREFERRED PRACTICE <sup>(1)</sup>
GPIO	DIO_n	5–12 14–21 NC or GND 26–32 36–43		NC
32.768-kHz crystal	X32K_Q1	3	3 NC or GND	
52.700-KI 12 CI yStal	X32K_Q2	4		NC
DC/DC converter <sup>(2)</sup>	DCDC_SW	33	NC (GND) <sup>(3)</sup>	NC (GND) <sup>(3)</sup>
	VDDS_DCDC	34	VDDS (GND) <sup>(3)</sup>	VDDS (GND) <sup>(3)</sup>

(1) NC = No connect

(2) When the DC/DC converter is not used, the inductor between DCDC\_SW and VDDR can be removed. VDDR and VDDR\_RF must still be connected and the 22 uF DCDC capacitor must be kept on the VDDR net.

(3) When operating in external regulator mode.



# **7** Specifications

## 7.1 Absolute Maximum Ratings

over operating free-air temperature range (unless otherwise noted)<sup>(1)</sup> (2)

			MIN	MAX	UNIT
VDDS <sup>(3)</sup>	Supply voltage		-0.3	4.1	V
VDDR <sup>((8))</sup>	Supply voltage (External	Supply voltage (External regulator mode)		2.25	V
	Voltage on any digital pin <sup>(5)</sup> <sup>(6)</sup>			VDDS + 0.3, max 4.1	V
	Voltage on crystal oscillator pins, X32K_Q1, X32K_Q2, X48M_N and X48M_P		-0.3	VDDR + 0.3, max 2.25	V
	Voltage scaling enabled		-0.3	VDDS	
Vin	Voltage on ADC input	Voltage scaling disabled, internal reference	-0.3	1.49	V
		Voltage scaling disabled, VDDS as reference	-0.3	VDDS / 2.9	
	Input level, RF pins (RF_P and RF_N)		dBm		
T <sub>stg</sub>	Storage temperature		-40	150	°C

(1) Operation outside the Absolute Maximum Ratings may cause permanent device damage. Absolute Maximum Ratings do not imply functional operation of the device at these or any other conditions beyond those listed under Recommended Operating Conditions. If used outside the Recommended Operating Conditions but within the Absolute Maximum Ratings, the device may not be fully functional, and this may affect device reliability, functionality, performance, and shorten the device lifetime

(2) All voltage values are with respect to ground, unless otherwise noted.

- (3) VDDS DCDC, VDDS2 and VDDS3 must be at the same potential as VDDS.
- (4) VDDR, VDDS, VDDS2 and VDDS3 must be at the same potential.
- (5) Including analog capable DIOs.
- (6) Injection current is not supported on any GPIO pin

### 7.2 ESD Ratings

			VALUE	UNIT
V <sub>ESD</sub> Electrostatic discharg	Human body model (HBM), per ANSI/ESDA/JEDEC JS-001 <sup>(1)</sup>	All pins	±2000	V
	Charged device model (CDM), per ANSI/ESDA/JEDEC JS-002 <sup>(2)</sup>	All pins	±500	V

(1) JEDEC document JEP155 states that 500-V HBM allows safe manufacturing with a standard ESD control process

(2) JEDEC document JEP157 states that 250-V CDM allows safe manufacturing with a standard ESD control process

# 7.3 Recommended Operating Conditions

over operating free-air temperature range (unless otherwise noted)

		MIN	MAX	UNIT
Operating ambient temperature <sup>(1) (3)</sup>			105	°C
Operating junction temperature <sup>(href)</sup> (href)			115	°C
Operating supply voltage (VDDS and VDDR), external regulator mode	For operation in 1.8-V systems (VDDS and VDDR pins connected on PCB, internal DC-DC cannot be used)	1.7	1.95	V
Operating supply voltage (VDDS)			3.8	V
Rising supply voltage slew rate		0	100	mV/μs
Falling supply voltage slew rate <sup>(2)</sup>		0	20	mV/μs

(1) Operation at or near maximum operating temperature for extended durations will result in a reduction in lifetime.

(2) For small coin-cell batteries, with high worst-case end-of-life equivalent source resistance, a 22-µF VDDS input capacitor must be used to ensure compliance with this slew rate.

(3) For thermal resistance characteristics refer to  $\frac{1}{2}222$  7.8.

### 7.4 Power Supply and Modules

over operating free-air temperature range (unless otherwise noted)

PARAMETER		MIN	TYP	MAX	UNIT
VDDS Power-on-Reset (POR) threshold		1	1 - 1.55		V
VDDS Brown-out Detector (BOD) <sup>(1)</sup>	Rising threshold		1.77		V

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# 7.4 Power Supply and Modules (continued)

over operating free-air temperature range (unless otherwise noted)

PARAMETER		MIN	TYP	MAX	UNIT
VDDS Brown-out Detector (BOD) External regulator mode	Rising threshold		1.64		V
VDDS Brown-out Detector (BOD), before initial boot <sup>(2)</sup>	Rising threshold		1.70		V
VDDS Brown-out Detector (BOD) <sup>(1)</sup>	Falling threshold		1.75		V
VDDS Brown-out Detector (BOD) External regulator mode	Falling threshold		1.63		V

(1) For boost mode (VDDR =1.95 V), TI drivers software initialization will trim VDDS BOD limits to maximum (approximately 2.0 V)

(2) Brown-out Detector is trimmed at initial boot, value is kept until device is reset by a POR reset or the RESET\_N pin



# 7.5 Power Consumption - Power Modes

When measured on the CC26x2-R7EM-7ID reference design with T<sub>c</sub> = 25 °C, V<sub>DDS</sub> = 3.0 V with DC/DC enabled unless otherwise noted.

PARAMETER		TEST CONDITIONS	ТҮР	UNIT
Core Curre	ent Consumption			
	Reset and Shutdown	Reset. RESET_N pin asserted or VDDS below power-on-reset threshold	100	-
	Reset and Shuldown	Shutdown. No clocks running, no retention	100	nA
		RTC running, CPU, 144KB RAM and (partial) register retention. RCOSC_LF	0.9	μA
	Standby without cache retention	RTC running, CPU, 64KB RAM and (partial) register retention. RCOSC_LF	0.8	μA
I <sub>core</sub>		RTC running, CPU, 144KB RAM and (partial) register retention XOSC_LF	1.0	μA
Standby with cache retention	Standby	RTC running, CPU, 144KB RAM and (partial) register retention. RCOSC_LF	2.3	μA
	with cache retention	RTC running, CPU, 144KB RAM and (partial) register retention. XOSC_LF	2.4	μA
	Idle	Supply Systems and RAM powered RCOSC_HF	669	μA
I <sub>core</sub>	Active	MCU running CoreMark at 48 MHz RCOSC_HF	3.1	mA
Peripheral	Current Consumption		1	
	Peripheral power domain	Delta current with domain enabled	49	
	Serial power domain	Delta current with domain enabled	3.6	
	RF Core	Delta current with power domain enabled, clock enabled, RF core idle	109	
	μDMA	Delta current with clock enabled, module is idle	69	
	Timers	Delta current with clock enabled, module is idle <sup>(3)</sup>	115	
I <sub>peri</sub>	12C	Delta current with clock enabled, module is idle	11.6	μA
	12S	Delta current with clock enabled, module is idle	27.6	
	SSI	Delta current with clock enabled, module is idle	61	
	UART	Delta current with clock enabled, module is idle <sup>(1)</sup>	131	
	CRYPTO (AES)	Delta current with clock enabled, module is idle <sup>(2)</sup>	19.5	
РКА		Delta current with clock enabled, module is idle	70	
	TRNG	Delta current with clock enabled, module is idle	25	
Sensor Co	ntroller Engine Consumption			
	Active mode	24 MHz, infinite loop	799	
I <sub>SCE</sub>	Low-power mode	/-power mode 2 MHz, infinite loop	29.2	μA

Only one UART running Only one SSI running (1)

(2)

(3) Only one GPTimer running



# 7.6 Power Consumption - Radio Modes

When measured on the CC26x2-R7EM-7ID reference design with  $T_c$  = 25 °C,  $V_{DDS}$  = 3.0 V with DC/DC enabled unless otherwise noted.

PARAM	IETER	TEST CONDITIONS	TYP	UNIT
Radio receiv	ve current	2440 MHz	6.4	mA
Radio transi	Radio transmit current 2.4 GHz PA (Bluetooth Low Energy)	0 dBm output power setting 2440 MHz	7.3	mA
2.4 GHz PA		+5 dBm output power setting 2440 MHz	9.7	mA

# 7.7 Nonvolatile (Flash) Memory Characteristics

Over operating free-air temperature range and  $V_{DDS} = 3.0 \text{ V}$  (unless otherwise noted)

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Flash sector size			8		KB
Supported flash erase cycles before failure, single-bank <sup>(1) (5)</sup>		30			k Cycles
Supported flash erase cycles before failure, single sector <sup>(2)</sup>		60			k Cycles
Maximum number of write operations per row before sector $\ensuremath{erase}^{(3)}$				83	Write Operations
Flash retention	105 °C	11.4			Years
Flash sector erase current	Average delta current		9.5		mA
Flash sector erase time <sup>(4)</sup>	Zero cycles		10		ms
Flash sector erase time	30k cycles			4000	ms
Flash write current	Average delta current, 4 bytes at a time		5.2		mA
Flash write time <sup>(4)</sup>	4 bytes at a time		21.6		μs

(1) A full bank erase is counted as a single erase cycle on each sector. If both flash banks are always cycled simultaneously they can be cycled 30K times each. Alternatively, the banks can be cycled a total of 30K times, e.g. the main bank X times and the second bank Y times (X+Y=30K)

(2) Up to 4 customer-designated sectors can be individually erased an additional 30k times beyond the baseline bank limitation of 30k cycles

(3) Each wordline is 2048 bits (or 256 bytes) wide. This limitation corresponds to sequential memory writes of 4 (3.1) bytes minimum per write over a whole wordline. If additional writes to the same wordline are required, a sector erase is required once the maximum number of write operations per row is reached.

(4) This number is dependent on Flash aging and increases over time and erase cycles

(5) Aborting flash during erase or program modes is not a safe operation.

# 7.8 Thermal Resistance Characteristics

		PACKAGE	
THERMAL METRIC <sup>(1)</sup>		RGZ (VQFN)	UNIT
		48 PINS	
R <sub>0JA</sub>	Junction-to-ambient thermal resistance	23.7	°C/W <sup>(2)</sup>
R <sub>0JC(top)</sub>	Junction-to-case (top) thermal resistance	13.0	°C/W <sup>(2)</sup>
R <sub>0JB</sub>	Junction-to-board thermal resistance	7.7	°C/W <sup>(2)</sup>
Ψυτ	Junction-to-top characterization parameter	0.1	°C/W <sup>(2)</sup>
Ψ <sub>JB</sub>	Junction-to-board characterization parameter	7.6	°C/W <sup>(2)</sup>
R <sub>0JC(bot)</sub>	Junction-to-case (bottom) thermal resistance	1.9	°C/W <sup>(2)</sup>

(1) For more information about traditional and new thermal metrics, see Semiconductor and IC Package Thermal Metrics.

(2) °C/W = degrees Celsius per watt.



# 7.9 RF Frequency Bands

Over operating free-air temperature range (unless otherwise noted).

PARAMETER	MIN	ТҮР	MAX	UNIT
Frequency bands	2360		2500	MHz



# 7.10 Bluetooth Low Energy - Receive (RX)

When measured on the CC26x2R-7EM-7ID reference design with  $T_c = 25$  °C,  $V_{DDS} = 3.0$  V,  $f_{RF} = 2440$  MHz with DC/DC enabled unless otherwise noted. All measurements are performed at the antenna input with a combined RX and TX path. All measurements are performed conducted.

PARAMETER	TEST CONDITIONS	MIN TYP		UNIT
125 kbps (LE Coded)				
Receiver sensitivity	Differential mode. BER = 10 <sup>-3</sup>	-104		dBm
Receiver saturation	Differential mode. BER = 10 <sup>-3</sup>	>5		dBm
Frequency error tolerance	Difference between the incoming carrier frequency and the internally generated carrier frequency	> (-300 / 300)		kHz
Data rate error tolerance	Difference between incoming data rate and the internally generated data rate (37-byte packets)	> (-320 / 240)		ppm
Data rate error tolerance	Difference between incoming data rate and the internally generated data rate (255-byte packets)	> (-125 / 100)		ppm
Co-channel rejection <sup>(1)</sup>	Wanted signal at –79 dBm, modulated interferer in channel, BER = $10^{-3}$	-1.5		dB
Selectivity, ±1 MHz <sup>(1)</sup>	Wanted signal at –79 dBm, modulated interferer at ±1 MHz, BER = $10^{-3}$	8 / 4.5 <sup>(2)</sup>		dB
Selectivity, ±2 MHz <sup>(1)</sup>	Wanted signal at –79 dBm, modulated interferer at ±2 MHz, BER = $10^{-3}$	44 / 37 <sup>(2)</sup>		dB
Selectivity, ±3 MHz <sup>(1)</sup>	Wanted signal at –79 dBm, modulated interferer at ±3 MHz, BER = $10^{-3}$	46 / 44 <sup>(2)</sup>		dB
Selectivity, ±4 MHz <sup>(1)</sup>	Wanted signal at –79 dBm, modulated interferer at ±4 MHz, BER = $10^{-3}$	44 / 46 <sup>(2)</sup>		dB
Selectivity, ±6 MHz <sup>(1)</sup>	Wanted signal at –79 dBm, modulated interferer at $\geq \pm 6$ MHz, BER = $10^{-3}$	48 / 44 <sup>(2)</sup>		dB
Selectivity, ±7 MHz	Wanted signal at –79 dBm, modulated interferer at $\geq \pm 7$ MHz, BER = $10^{-3}$	51 / 45 <sup>(2)</sup>		dB
Selectivity, Image frequency <sup>(1)</sup>	Wanted signal at –79 dBm, modulated interferer at image frequency, BER = $10^{-3}$	37		dB
Selectivity, Image frequency ±1 MHz <sup>(1)</sup>	Note that Image frequency + 1 MHz is the Co- channel – 1 MHz. Wanted signal at –79 dBm, modulated interferer at $\pm$ 1 MHz from image frequency, BER = $10^{-3}$	4.5 / 44 <sup>(2)</sup>		dB
RSSI Range		89		dB
RSSI Accuracy (+/-)		±4		dB
500 kbps (LE Coded)	· · · · ·			
Receiver sensitivity	Differential mode. BER = 10 <sup>-3</sup>	-100		dBm
Receiver saturation	Differential mode. BER = 10 <sup>-3</sup>	> 5		dBm
Frequency error tolerance	Difference between the incoming carrier frequency and the internally generated carrier frequency	> (-300 / 300)		kHz
Data rate error tolerance	Difference between incoming data rate and the internally generated data rate (37-byte packets)	> (-450 / 450)		ppm
Data rate error tolerance	Difference between incoming data rate and the internally generated data rate (255-byte packets)	> (-150 / 175)		ppm
Co-channel rejection <sup>(1)</sup>	Wanted signal at $-72$ dBm, modulated interferer in channel, BER = $10^{-3}$	-3.5		dB
Selectivity, ±1 MHz <sup>(1)</sup>	Wanted signal at –72 dBm, modulated interferer at ±1 MHz, BER = $10^{-3}$	8 / 4 <sup>(2)</sup>		dB
Selectivity, ±2 MHz <sup>(1)</sup>	Wanted signal at –72 dBm, modulated interferer at $\pm 2$ MHz, BER = $10^{-3}$	43 / 35 <sup>(2)</sup>		dB
Selectivity, ±3 MHz <sup>(1)</sup>	Wanted signal at –72 dBm, modulated interferer at ±3 MHz, BER = $10^{-3}$	46 / 46 <sup>(2)</sup>		dB
Selectivity, ±4 MHz <sup>(1)</sup>	Wanted signal at –72 dBm, modulated interferer at ±4 MHz, BER = $10^{-3}$	45 / 47 <sup>(2)</sup>		dB
Selectivity, ±6 MHz <sup>(1)</sup>	Wanted signal at –72 dBm, modulated interferer at $\ge \pm 6$ MHz, BER = $10^{-3}$	46 / 45 <sup>(2)</sup>		dB
Selectivity, ±7 MHz	Wanted signal at –72 dBm, modulated interferer at $\geq \pm 7$ MHz, BER = $10^{-3}$	49 / 45 <sup>(2)</sup>		dB



# 7.10 Bluetooth Low Energy - Receive (RX) (continued)

When measured on the CC26x2R-7EM-7ID reference design with  $T_c = 25$  °C,  $V_{DDS} = 3.0$  V,  $f_{RF} = 2440$  MHz with DC/DC enabled unless otherwise noted. All measurements are performed at the antenna input with a combined RX and TX path. All measurements are performed conducted.

PARAMETER	TEST CONDITIONS	MIN TYP	MAX UNIT
Selectivity, Image frequency <sup>(1)</sup>	Wanted signal at $-72$ dBm, modulated interferer at image frequency, BER = $10^{-3}$	35	dB
Selectivity, Image frequency $\pm 1 \ MHz^{(1)}$	Note that Image frequency + 1 MHz is the Co- channel – 1 MHz. Wanted signal at –72 dBm, modulated interferer at $\pm$ 1 MHz from image frequency, BER = $10^{-3}$	4 / 46 <sup>(2)</sup>	dB
RSSI Range		90	dB
RSSI Accuracy (+/-)		±4	dB
1 Mbps (LE 1M)			
Receiver sensitivity	Differential mode. BER = $10^{-3}$	-97	dBm
Receiver saturation	Differential mode. BER = $10^{-3}$	> 5	dBm
Frequency error tolerance	Difference between the incoming carrier frequency and the internally generated carrier frequency	> (-350 / 350)	kHz
Data rate error tolerance	Difference between incoming data rate and the internally generated data rate (37-byte packets)	> (-650 / 750)	ppm
Co-channel rejection <sup>(1)</sup>	Wanted signal at –67 dBm, modulated interferer in channel, BER = $10^{-3}$	-6	dB
Selectivity, ±1 MHz <sup>(1)</sup>	Wanted signal at –67 dBm, modulated interferer at ±1 MHz, BER = $10^{-3}$	7 / 4 <sup>(2)</sup>	dB
Selectivity, ±2 MHz <sup>(1)</sup>	Wanted signal at –67 dBm, modulated interferer at $\pm 2$ MHz,BER = $10^{-3}$	39 / 33 <sup>(2)</sup>	dB
Selectivity, ±3 MHz <sup>(1)</sup>	Wanted signal at –67 dBm, modulated interferer at $\pm 3$ MHz, BER = $10^{-3}$	36 / 40 <sup>(2)</sup>	dB
Selectivity, ±4 MHz <sup>(1)</sup>	Wanted signal at –67 dBm, modulated interferer at $\pm 4$ MHz, BER = $10^{-3}$	36 / 45 <sup>(2)</sup>	dB
Selectivity, ±5 MHz or more <sup>(1)</sup>	Wanted signal at –67 dBm, modulated interferer at $\geq \pm 5$ MHz, BER = $10^{-3}$	40	dB
Selectivity, image frequency <sup>(1)</sup>	Wanted signal at –67 dBm, modulated interferer at image frequency, BER = $10^{-3}$	33	dB
Selectivity, image frequency ±1 MHz <sup>(1)</sup>	Note that Image frequency + 1 MHz is the Co- channel – 1 MHz. Wanted signal at $-67$ dBm, modulated interferer at $\pm 1$ MHz from image frequency, BER = $10^{-3}$	4 / 41 <sup>(2)</sup>	dB
Out-of-band blocking <sup>(3)</sup>	30 MHz to 2000 MHz	-10	dBm
Out-of-band blocking	2003 MHz to 2399 MHz	-18	dBm
Out-of-band blocking	2484 MHz to 2997 MHz	-12	dBm
Out-of-band blocking	3000 MHz to 12.75 GHz	-2	dBm
Intermodulation	Wanted signal at 2402 MHz, –64 dBm. Two interferers at 2405 and 2408 MHz respectively, at the given power level	-42	dBm
Spurious emissions, 30 to 1000 MHz	Measurement in a 50- $\Omega$ single-ended load.	< -59	dBm
Spurious emissions, 1 to 12.75 GHz	Measurement in a 50- $\Omega$ single-ended load.	<-47	dBm
RSSI dynamic range		70	dB
RSSI accuracy		±4	dB
2 Mbps (LE 2M)			
Receiver sensitivity	Differential mode. Measured at SMA connector, BER = $10^{-3}$	-91	dBm
Receiver saturation	Differential mode. Measured at SMA connector, BER = $10^{-3}$	> 5	dBm
Frequency error tolerance	Difference between the incoming carrier frequency and the internally generated carrier frequency	> (-500 / 500)	kHz
Data rate error tolerance	Difference between incoming data rate and the internally generated data rate (37-byte packets)	> (-700 / 750)	ppm



# 7.10 Bluetooth Low Energy - Receive (RX) (continued)

When measured on the CC26x2R-7EM-7ID reference design with  $T_c = 25$  °C,  $V_{DDS} = 3.0$  V,  $f_{RF} = 2440$  MHz with DC/DC enabled unless otherwise noted. All measurements are performed at the antenna input with a combined RX and TX path. All measurements are performed conducted.

PARAMETER	TEST CONDITIONS	MIN	ТҮР	MAX	UNIT
Co-channel rejection <sup>(1)</sup>	Wanted signal at –67 dBm, modulated interferer in channel,BER = 10 <sup>-3</sup>		-7		dB
Selectivity, ±2 MHz <sup>(1)</sup>	Wanted signal at –67 dBm, modulated interferer at $\pm 2$ MHz, Image frequency is at –2 MHz, BER = $10^{-3}$		8 / 4 <sup>(2)</sup>		dB
Selectivity, ±4 MHz <sup>(1)</sup>	Wanted signal at –67 dBm, modulated interferer at ±4 MHz, BER = $10^{-3}$		36 / 34 <sup>(2)</sup>		dB
Selectivity, ±6 MHz <sup>(1)</sup>	Wanted signal at –67 dBm, modulated interferer at $\pm 6$ MHz, BER = $10^{-3}$	37 / 36 <sup>(2)</sup>			dB
Selectivity, image frequency <sup>(1)</sup>	Wanted signal at –67 dBm, modulated interferer at image frequency, BER = $10^{-3}$	·	4		dB
Selectivity, image frequency ±2 MHz <sup>(1)</sup>	Note that Image frequency + 2 MHz is the Co-channel. Wanted signal at $-67$ dBm, modulated interferer at $\pm 2$ MHz from image frequency, BER = $10^{-3}$		-7 / 36 <sup>(2)</sup>		dB
Out-of-band blocking <sup>(3)</sup>	30 MHz to 2000 MHz		-16		dBm
Out-of-band blocking	2003 MHz to 2399 MHz		-21		dBm
Out-of-band blocking	2484 MHz to 2997 MHz		-15		dBm
Out-of-band blocking	3000 MHz to 12.75 GHz		-12		dBm
Intermodulation	Wanted signal at 2402 MHz, –64 dBm. Two interferers at 2408 and 2414 MHz respectively, at the given power level		-38		dBm
RSSI Range			60		dB
RSSI Accuracy (+/-)			±4		dB

(1) Numbers given as I/C dB

(2) X / Y, where X is +N MHz and Y is –N MHz

(3) Excluding one exception at  $F_{wanted}$  / 2, per Bluetooth Specification



# 7.11 Bluetooth Low Energy - Transmit (TX)

When measured on the CC26x2-R7EM-7ID reference design with  $T_c = 25$  °C,  $V_{DDS} = 3.0$  V,  $f_{RF} = 2440$  MHz with DC/DC enabled unless otherwise noted. All measurements are performed at the antenna input with a combined RX and TX path. All measurements are performed conducted.

PARAMETER		TEST CONDITIONS	MIN TYP	MAX	UNIT
General Parameters					
Max output power	<i>l</i> ax output power Differential mode, delivered to a single-ended 50 $\Omega$ load through a balun				dBm
Output power programmable range	Differential mode, delivered to a sing	Differential mode, delivered to a single-ended 50 $\Omega$ load through a balun			dB
Spurious emissions	and harmonics				
	f < 1 GHz, outside restricted bands		< -36		dBm
Country on the starts	f < 1 GHz, restricted bands ETSI		<54		dBm
Spurious emissions	f < 1 GHz, restricted bands FCC		<55		dBm
	f > 1 GHz, including harmonics	+5 dBm setting	< -42		dBm
Harmonics	Second harmonic	-	< -42		dBm
	Third harmonic		< -42		dBm



# 7.12 Zigbee and Thread - IEEE 802.15.4-2006 2.4 GHz (OQPSK DSSS1:8, 250 kbps) - RX

When measured on the CC26x2-R7EM-7ID reference design with  $T_c = 25$  °C,  $V_{DDS} = 3.0$  V,  $f_{RF} = 2440$  MHz with DC/DC enabled unless otherwise noted. All measurements are performed at the antenna input with a combined RX and TX path. All measurements are performed conducted.

PARAMETER	TEST CONDITIONS	MIN	TYP MAX	UNIT
General Parameters				
Receiver sensitivity	PER = 1%		-99	dBm
Receiver saturation	PER = 1%		> 5	dBm
Adjacent channel rejection	Wanted signal at –82 dBm, modulated interferer at $\pm$ 5 MHz, PER = 1%	36		dB
Alternate channel rejection	Wanted signal at –82 dBm, modulated interferer at ±10 MHz, PER = $1\%$		57	dB
Channel rejection, ±15 MHz or more	Wanted signal at –82 dBm, undesired signal is IEEE 802.15.4 modulated channel, stepped through all channels 2405 to 2480 MHz, PER = 1%	59		dB
Blocking and desensitization, 5 MHz from upper band edge	Wanted signal at –97 dBm (3 dB above the sensitivity level), CW jammer, PER = 1%		57	dB
Blocking and desensitization, 10 MHz from upper band edge	Wanted signal at –97 dBm (3 dB above the sensitivity level), CW jammer, PER = 1%		62	dB
Blocking and desensitization, 20 MHz from upper band edge	Wanted signal at –97 dBm (3 dB above the sensitivity level), CW jammer, PER = 1%		62	dB
Blocking and desensitization, 50 MHz from upper band edge	Wanted signal at –97 dBm (3 dB above the sensitivity level), CW jammer, PER = 1%	65		dB
Blocking and desensitization, –5 MHz from lower band edge	Wanted signal at –97 dBm (3 dB above the sensitivity level), CW jammer, PER = 1%	59		dB
Blocking and desensitization, –10 MHz from lower band edge	Wanted signal at –97 dBm (3 dB above the sensitivity level), CW jammer, PER = 1%		59	dB
Blocking and desensitization, –20 MHz from lower band edge	Wanted signal at –97 dBm (3 dB above the sensitivity level), CW jammer, PER = 1%		63	dB
Blocking and desensitization, –50 MHz from lower band edge	Wanted signal at –97 dBm (3 dB above the sensitivity level), CW jammer, PER = 1%		65	dB
Spurious emissions, 30 MHz to 1000 MHz	Measurement in a 50- $\Omega$ single-ended load		-66	dBm
Spurious emissions, 1 GHz to 12.75 GHz	Measurement in a 50- $\Omega$ single-ended load		-53	dBm
Frequency error tolerance	Difference between the incoming carrier frequency and the internally generated carrier frequency	>	350	ppm
Symbol rate error tolerance	Difference between incoming symbol rate and the internally generated symbol rate	> 1	1000	ppm
RSSI dynamic range			95	dB
RSSI accuracy			±4	dB



# 7.13 Zigbee and Thread - IEEE 802.15.4-2006 2.4 GHz (OQPSK DSSS1:8, 250 kbps) - TX

When measured on the CC26x2-R7EM-7ID reference design with  $T_c = 25$  °C,  $V_{DDS} = 3.0$  V,  $f_{RF} = 2440$  MHz with DC/DC enabled unless otherwise noted. All measurements are performed at the antenna input with a combined RX and TX path. All measurements are performed conducted.

PARAMETER		TEST CONDITIONS		MAX UNIT
General Parameters				
Max output power	Differential mode, delivered to a si	ngle-ended 50-Ω load through a balun	5	dBm
Output power programmable range	Differential mode, delivered to a si	ferential mode, delivered to a single-ended 50- $\Omega$ load through a balun		dB
Spurious emissions an	d harmonics			
	f < 1 GHz, outside restricted bands	+5 dBm setting	< -36	dBm
Spurious emissions <sup>(1)</sup>	f < 1 GHz, restricted bands ETSI		< -47	dBm
	f < 1 GHz, restricted bands FCC		< -55	dBm
	f > 1 GHz, including harmonics		< -42	dBm
	Second harmonic		< -42	dBm
Harmonics	Third harmonic		< -42	dBm
IEEE 802.15.4-2006 2.4	GHz (OQPSK DSSS1:8, 250 kbps)	•		
Error vector magnitude	+5 dBm setting		2	%

(1) To ensure margins for passing FCC band edge requirements at 2483.5 MHz, a lower than maximum output-power setting or less than 100% duty cycle may be used when operating at 2480 MHz.

## 7.14 Timing and Switching Characteristics

#### 7.14.1 Reset Timing

PARAMETER	MIN	TYP	MAX	UNIT
RESET_N low duration	1			μs

### 7.14.2 Wakeup Timing

Measured over operating free-air temperature with  $V_{DDS}$  = 3.0 V (unless otherwise noted). The times listed here do not include software overhead.

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
MCU, Reset to Active <sup>(1)</sup>		8	350 - 4000		μs
MCU, Shutdown to Active <sup>(1)</sup>		8	350 - 4000		μs
MCU, Standby to Active			165		μs
MCU, Active to Standby			39		μs
MCU, Idle to Active			15		μs

(1) The wakeup time is dependent on remaining charge on VDDR capacitor when starting the device, and thus how long the device has been in Reset or Shutdown before starting up again. The wake up time increases with a higher capacitor value.



#### 7.14.3 Clock Specifications

#### 7.14.3.1 48 MHz Crystal Oscillator (XOSC\_HF)

Measured on a Texas Instruments reference design with  $T_c = 25 \degree C$ ,  $V_{DDS} = 3.0 \lor V$ , unless otherwise noted.<sup>(1)</sup>

	PARAMETER	MIN	TYP	MAX	UNIT
	Crystal frequency		48		MHz
ESR	Equivalent series resistance 6 pF < C <sub>L</sub> ≤ 9 pF		20	60	Ω
ESR	Equivalent series resistance 5 pF < $C_L \leq 6 pF$			80	Ω
L <sub>M</sub>	Motional inductance, relates to the load capacitance that is used for the crystal (CL in Farads) $^{(5)}$		$< 3 \times 10^{-25}$ / C <sub>L</sub> <sup>2</sup>		н
CL	Crystal load capacitance <sup>(4)</sup>	5	7 <sup>(3)</sup>	9	pF
	Start-up time <sup>(2)</sup>		200		μs

(1) Probing or otherwise stopping the crystal while the DC/DC converter is enabled may cause permanent damage to the device.

(2) Start-up time using the TI-provided power driver. Start-up time may increase if driver is not used.

(3) On-chip default connected capacitance including reference design parasitic capacitance. Connected internal capacitance is changed through software in the Customer Configuration section (CCFG).

- (4) Adjustable load capacitance is integrated into the device.
- (5) The crystal manufacturer's specification must satisfy this requirement for proper operation.

# 7.14.3.2 48 MHz RC Oscillator (RCOSC\_HF)

Measured on a Texas Instruments reference design with T<sub>c</sub> = 25 °C, V<sub>DDS</sub> = 3.0 V, unless otherwise noted.

	MIN	TYP	MAX	UNIT
Frequency		48		MHz
Uncalibrated frequency accuracy		±1		%
Calibrated frequency accuracy <sup>(1)</sup>		±0.25		%
Start-up time		5		μs

(1) Accuracy relative to the calibration source (XOSC\_HF)

### 7.14.3.3 2 MHz RC Oscillator (RCOSC\_MF)

Measured on a Texas Instruments reference design with  $T_c = 25$  °C,  $V_{DDS} = 3.0$  V, unless otherwise noted.

	MIN	TYP	MAX	UNIT
Calibrated frequency		2		MHz
Start-up time		5		μs

### 7.14.3.4 32.768 kHz Crystal Oscillator (XOSC\_LF)

Measured on a Texas Instruments reference design with  $T_c$  = 25 °C,  $V_{DDS}$  = 3.0 V, unless otherwise noted.

		MIN	TYP	MAX	UNIT
	Crystal frequency		32.768		kHz
ESR	Equivalent series resistance		30	100	kΩ
CL	Crystal load capacitance	6	7 <sup>(1)</sup>	12	pF

(1) Default load capacitance using TI reference designs including parasitic capacitance. Crystals with different load capacitance may be used.

### 7.14.3.5 32 kHz RC Oscillator (RCOSC\_LF)

Measured on a Texas Instruments reference design with  $T_c$  = 25 °C,  $V_{DDS}$  = 3.0 V, unless otherwise noted.

		MIN	TYP	MAX	UNIT
Frequency			32.8		kHz
Calibrated RTC variation <sup>((1))</sup>	Calibrated periodically against XOSC_HF <sup>(2)</sup>		±600 <sup>(3)</sup>		ppm



## 7.14.3.5 32 kHz RC Oscillator (RCOSC\_LF) (continued)

Measured on a Texas Instruments reference design with  $T_c$  = 25 °C,  $V_{DDS}$  = 3.0 V, unless otherwise noted.

	MIN	TYP	MAX	UNIT
Temperature coefficient		50		ppm/°C

(1) When using RCOSC\_LF as source for the low frequency system clock (SCLK\_LF), the accuracy of the SCLK\_LF-derived Real Time Clock (RTC) can be improved by measuring RCOSC\_LF relative to XOSC\_HF and compensating for the RTC tick speed. This functionality is available through the TI-provided Power driver.

(2) TI driver software calibrates the RTC every time XOSC\_HF is enabled.

(3) Some device's variation can exceed 1000 ppm. Further calibration will not improve variation.

#### 7.14.4 Synchronous Serial Interface (SSI) Characteristics

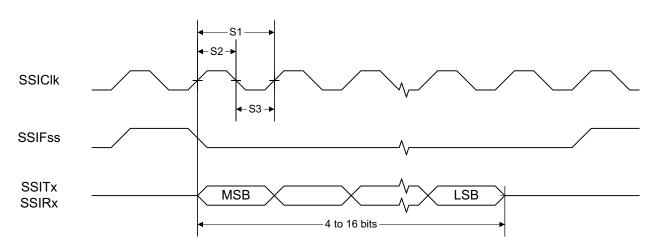
#### 7.14.4.1 Synchronous Serial Interface (SSI) Characteristics

over operating free-air temperature range (unless otherwise noted)

PARAMETER NO.		PARAMETER	MIN	TYP	МАХ	UNIT
S1	t <sub>clk_per</sub>	SSIClk cycle time	12	·	65024	System Clocks <sup>(2)</sup>
S2 <sup>(1)</sup>	t <sub>clk_high</sub>	SSIClk high time		0.5		t <sub>clk_per</sub>
S3 <sup>(1)</sup>	t <sub>clk_low</sub>	SSIClk low time		0.5		t <sub>clk_per</sub>

(1) Refer to SSI timing diagrams ⊠ 7-1, ⊠ 7-2 and ⊠ 7-3.

(2) When using the TI-provided Power driver, the SSI system clock is always 48 MHz.



#### 図 7-1. SSI Timing for TI Frame Format (FRF = 01), Single Transfer Timing Measurement



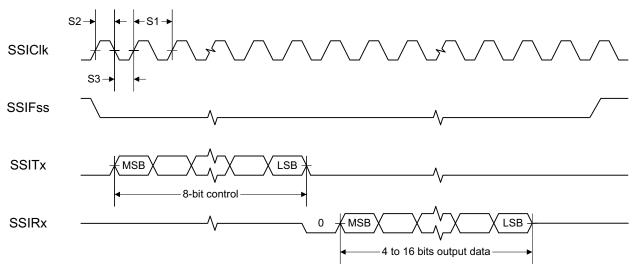
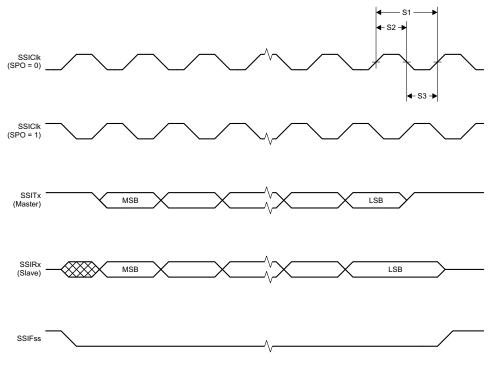


図 7-2. SSI Timing for MICROWIRE Frame Format (FRF = 10), Single Transfer





# 7.14.5 UART 7.14.5.1 UART Characteristics

over operating free-air temperature range (unless otherwise noted)

PARAMETER	MIN	TYP	MAX	UNIT
UART rate			2.89	MBaud



# 7.15 Peripheral Characteristics

## 7.15.1 ADC

### 7.15.1.1 Analog-to-Digital Converter (ADC) Characteristics

 $T_c = 25 \text{ °C}$ ,  $V_{DDS} = 3.0 \text{ V}$  and voltage scaling enabled, unless otherwise noted.<sup>((1))</sup> Performance numbers require use of offset and gain adjustments in software by TI-provided ADC drivers.

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
	Input voltage range		0		VDDS	V
	Resolution			12		Bits
	Sample Rate				200	ksps
	Offset	Internal 4.3 V equivalent reference <sup>(2)</sup>		±2		LSB
	Gain error	Internal 4.3 V equivalent reference <sup>(2)</sup>		±7		LSB
DNL <sup>(4)</sup>	Differential nonlinearity			>–1		LSB
NL	Integral nonlinearity			±4		LSB
		Internal 4.3 V equivalent reference <sup>(2)</sup> , 200 kSamples/s, 9.6 kHz input tone		9.8		
		Internal 4.3 V equivalent reference <sup>(2)</sup> , 200 kSamples/s, 9.6 kHz input tone, DC/DC enabled		9.8		
		VDDS as reference, 200 kSamples/s, 9.6 kHz input tone		10.1		
ENOB	Effective number of bits	Internal reference, voltage scaling disabled, 32 samples average, 200 kSamples/s, 300 Hz input tone		11.1		Bits
		Internal reference, voltage scaling disabled, 14-bit mode, 200 kSamples/s, 600 Hz input tone <sup>((5))</sup>		11.3		
		Internal reference, voltage scaling disabled, 15-bit mode, 200 kSamples/s, 150 Hz input tone <sup>((5))</sup>		11.6		
		Internal 4.3 V equivalent reference <sup>(2)</sup> , 200 kSamples/s, 9.6 kHz input tone		-65		
THD	Total harmonic distortion	VDDS as reference, 200 kSamples/s, 9.6 kHz input tone		-70		dB
		Internal reference, voltage scaling disabled, 32 samples average, 200 kSamples/s, 300 Hz input tone		-72		
	Signal-to-noise	Internal 4.3 V equivalent reference <sup>(2)</sup> , 200 kSamples/s, 9.6 kHz input tone		60		
SINAD, SNDR	and	VDDS as reference, 200 kSamples/s, 9.6 kHz input tone		63		dB
	distortion ratio	Internal reference, voltage scaling disabled, 32 samples average, 200 kSamples/s, 300 Hz input tone		68		
		Internal 4.3 V equivalent reference <sup>(2)</sup> , 200 kSamples/s, 9.6 kHz input tone		70		
SFDR	Spurious-free dynamic range	VDDS as reference, 200 kSamples/s, 9.6 kHz input tone		73		dB
		Internal reference, voltage scaling disabled, 32 samples average, 200 kSamples/s, 300 Hz input tone		75		
	Conversion time	Serial conversion, time-to-output, 24 MHz clock		50		Clock Cycles
	Current consumption	Internal 4.3 V equivalent reference <sup>(2)</sup>		0.40		mA
	Current consumption	VDDS as reference		0.57		mA
	Reference voltage	Equivalent fixed internal reference (input voltage scaling enabled). For best accuracy, the ADC conversion should be initiated through the TI-RTOS API in order to include the gain/ offset compensation factors stored in FCFG1	4	.3(2) (3)		V
	Reference voltage	Fixed internal reference (input voltage scaling disabled). For best accuracy, the ADC conversion should be initiated through the TI-RTOS API in order to include the gain/offset compensation factors stored in FCFG1. This value is derived from the scaled value (4.3 V) as follows: $V_{ref}$ = 4.3 V × 1408 / 4095		1.48		V
	Reference voltage	VDDS as reference, input voltage scaling enabled		VDDS		V
	Reference voltage	VDDS as reference, input voltage scaling disabled		′DDS / 2.82 <sup>(3)</sup>		V



## 7.15.1.1 Analog-to-Digital Converter (ADC) Characteristics (continued)

 $T_c = 25 \text{ °C}$ ,  $V_{DDS} = 3.0 \text{ V}$  and voltage scaling enabled, unless otherwise noted.<sup>((1))</sup> Performance numbers require use of offset and gain adjustments in software by TI-provided ADC drivers.

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Input impedance	200 kSamples/s, voltage scaling enabled. Capacitive input, Input impedance depends on sampling frequency and sampling time		>1		MΩ

(1) Using IEEE Std 1241-2010 for terminology and test methods

(2) Input signal scaled down internally before conversion, as if voltage range was 0 to 4.3 V

(3) Applied voltage must be within Absolute Maximum Ratings at all times

(4) No missing codes

(5) ADC\_output =  $\Sigma(4^n \text{ samples }) >> n, n = \text{desired extra bits}$ 

### 7.15.2 DAC

#### 7.15.2.1 Digital-to-Analog Converter (DAC) Characteristics

 $T_c$  = 25 °C,  $V_{DDS}$  = 3.0 V, unless otherwise noted.

	PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Genera	l Parameters	· /				
	Resolution			8		Bits
		Any load, any V <sub>REF</sub> , pre-charge OFF, DAC charge-pump ON	1.8		3.8	
V <sub>DDS</sub>	Supply voltage	External Load <sup>(4)</sup> , any $V_{REF}$ , pre-charge OFF, DAC charge-pump OFF	2.0		3.8	V
		Any load, V <sub>REF</sub> = DCOUPL, pre-charge ON	2.6		3.8	
-	Cleak fraguanau	Buffer ON (recommended for external load)	16		250	kHz
F <sub>DAC</sub>	Clock frequency	Buffer OFF (internal load)	16		1000	KLIZ
	Voltage output settling time	V <sub>REF</sub> = VDDS, buffer OFF, internal load		13		1/5
	voltage output settling time	$V_{REF}$ = VDDS, buffer ON, external capacitive load = 20 pF <sup>(3)</sup>		13.8		1 / F <sub>DAC</sub>
	External capacitive load			20	200	pF
	External resistive load		10			MΩ
	Short circuit current				400	μA
		VDDS = 3.8 V, DAC charge-pump OFF		50.8		
		VDDS = 3.0 V, DAC charge-pump ON		51.7		
	Max output impedance Vref =	VDDS = 3.0 V, DAC charge-pump OFF		53.2		kΩ
Z <sub>MAX</sub>	VDDS, buffer ON, CLK 250 kHz	VDDS = 2.0 V, DAC charge-pump ON		48.7		
		VDDS = 2.0 V, DAC charge-pump OFF		70.2		
		VDDS = 1.8 V, DAC charge-pump ON		46.3		
		VDDS = 1.8 V, DAC charge-pump OFF		88.9		
Internal	Load - Continuous Time Com	parator / Low Power Clocked Comparator				
Differential nonlinearity		$V_{REF}$ = VDDS, load = Continuous Time Comparator or Low Power Clocked Comparator $F_{DAC}$ = 250 kHz		±1		LSB <sup>(1)</sup>
DNL	Differential nonlinearity	V <sub>REF</sub> = VDDS, load = Continuous Time Comparator or Low Power Clocked Comparator F <sub>DAC</sub> = 16 kHz		±1.2		LOD
		V <sub>REF</sub> = VDDS = 3.8 V		±0.64		
		V <sub>REF</sub> = VDDS= 3.0 V		±0.81		
	Offset error <sup>(2)</sup> Load = Continuous Time	V <sub>REF</sub> = VDDS = 1.8 V		±1.27		LSB <sup>(1)</sup>
	Comparator	V <sub>REF</sub> = DCOUPL, pre-charge ON		±3.43		LOD
		V <sub>REF</sub> = DCOUPL, pre-charge OFF		±2.88		
		V <sub>REF</sub> = ADCREF		±2.37		



## 7.15.2.1 Digital-to-Analog Converter (DAC) Characteristics (continued)

 $T_c$  = 25 °C,  $V_{DDS}$  = 3.0 V, unless otherwise noted.

	PARAMETER	TEST CONDITIONS	MIN TYP MAX	UNIT
		V <sub>REF</sub> = VDDS= 3.8 V	±0.78	
		V <sub>REF</sub> = VDDS = 3.0 V	±0.77	
	Offset error <sup>(2)</sup> Load = Low Power Clocked	V <sub>REF</sub> = VDDS= 1.8 V	±3.46	LSB <sup>(1)</sup>
	Comparator	V <sub>REF</sub> = DCOUPL, pre-charge ON	±3.44	LOD
		V <sub>REF</sub> = DCOUPL, pre-charge OFF	±4.70	
		V <sub>REF</sub> = ADCREF	±4.11	
		V <sub>REF</sub> = VDDS = 3.8 V	±1.53	
	Max code output voltage	V <sub>REF</sub> = VDDS = 3.0 V	±1.71	
	variation <sup>(2)</sup>	V <sub>REF</sub> = VDDS= 1.8 V	±2.10	LSB <sup>(1)</sup>
	Load = Continuous Time Comparator	V <sub>REF</sub> = DCOUPL, pre-charge ON	±6.00	LOD
	Comparator	V <sub>REF</sub> = DCOUPL, pre-charge OFF	±3.85	
		V <sub>REF</sub> = ADCREF	±5.84	
		V <sub>REF</sub> = VDDS= 3.8 V	±2.92	
	Max and a output valtage	V <sub>REF</sub> =VDDS= 3.0 V	±3.06	
	Max code output voltage variation <sup>(2)</sup>	V <sub>REF</sub> = VDDS= 1.8 V	±3.91	LSB <sup>(1)</sup>
	Load = Low Power Clocked Comparator	V <sub>REF</sub> = DCOUPL, pre-charge ON	±7.84	LOD
	Comparator	V <sub>REF</sub> = DCOUPL, pre-charge OFF	±4.06	
		V <sub>REF</sub> = ADCREF	±6.94	
		V <sub>REF</sub> = VDDS = 3.8 V, code 1	0.03	
		V <sub>REF</sub> = VDDS = 3.8 V, code 255	3.62	
		V <sub>REF</sub> = VDDS= 3.0 V, code 1	0.02	
		V <sub>REF</sub> = VDDS= 3.0 V, code 255	2.86	
		V <sub>REF</sub> = VDDS= 1.8 V, code 1	0.01	
	Output voltage range <sup>(2)</sup>	V <sub>REF</sub> = VDDS = 1.8 V, code 255	1.71	
	Load = Continuous Time Comparator	V <sub>REF</sub> = DCOUPL, pre-charge OFF, code 1	0.01	V
		V <sub>REF</sub> = DCOUPL, pre-charge OFF, code 255	1.21	
		V <sub>REF</sub> = DCOUPL, pre-charge ON, code 1	1.27	
		V <sub>REF</sub> = DCOUPL, pre-charge ON, code 255	2.46	
		V <sub>REF</sub> = ADCREF, code 1	0.01	
		V <sub>REF</sub> = ADCREF, code 255	1.41	
		V <sub>REF</sub> = VDDS = 3.8 V, code 1	0.03	
		V <sub>REF</sub> = VDDS= 3.8 V, code 255	3.61	
		V <sub>REF</sub> = VDDS= 3.0 V, code 1	0.02	
		V <sub>REF</sub> = VDDS= 3.0 V, code 255	2.85	
		V <sub>REF</sub> = VDDS = 1.8 V, code 1	0.01	
	Output voltage range <sup>(2)</sup>	V <sub>REF</sub> = VDDS = 1.8 V, code 255	1.71	
	Load = Low Power Clocked Comparator	V <sub>REF</sub> = DCOUPL, pre-charge OFF, code 1	0.01	V
		V <sub>REF</sub> = DCOUPL, pre-charge OFF, code 255	1.21	
		V <sub>REF</sub> = DCOUPL, pre-charge ON, code 1	1.27	
		V <sub>REF</sub> = DCOUPL, pre-charge ON, code 255	2.46	
		V <sub>REF</sub> = ADCREF, code 1	0.01	
		V <sub>REF</sub> = ADCREF, code 255	1.41	
ernal	Load			
		V <sub>REF</sub> = VDDS, F <sub>DAC</sub> = 250 kHz	±1	
	Integral nonlinearity	V <sub>REF</sub> = DCOUPL, F <sub>DAC</sub> = 250 kHz	±2	LSB <sup>(1)</sup>
		$V_{\text{REF}}$ = ADCREF, F <sub>DAC</sub> = 250 kHz		
IL	Differential nonlinearity	$V_{\text{REF}} = VDDS, F_{DAC} = 250 \text{ kHz}$	±1	LSB <sup>(1)</sup>



# 7.15.2.1 Digital-to-Analog Converter (DAC) Characteristics (continued)

 $T_c$  = 25 °C,  $V_{DDS}$  = 3.0 V, unless otherwise noted.

PARAMETER	TEST CONDITIONS	MIN TYP	MAX	UNIT
	V <sub>REF</sub> = VDDS= 3.8 V	±0.40		
	V <sub>REF</sub> = VDDS= 3.0 V	±0.50		
Offset error	V <sub>REF</sub> = VDDS = 1.8 V	±0.75		LSB <sup>(1)</sup>
Oliset error	V <sub>REF</sub> = DCOUPL, pre-charge ON	±1.55		LOD
	V <sub>REF</sub> = DCOUPL, pre-charge OFF	±1.30		
	V <sub>REF</sub> = ADCREF	±1.10		
	V <sub>REF</sub> = VDDS= 3.8 V	±1.00		
	V <sub>REF</sub> = VDDS= 3.0 V	±1.00		
Max code output voltage	V <sub>REF</sub> = VDDS= 1.8 V	±1.00		LSB <sup>(1)</sup>
variation	V <sub>REF</sub> = DCOUPL, pre-charge ON	±3.45		LOD
	V <sub>REF</sub> = DCOUPL, pre-charge OFF	±2.10		
	V <sub>REF</sub> = ADCREF	±1.90		
	V <sub>REF</sub> = VDDS = 3.8 V, code 1	0.03		
	V <sub>REF</sub> = VDDS = 3.8 V, code 255	3.61		
	V <sub>REF</sub> = VDDS = 3.0 V, code 1	0.02		
	V <sub>REF</sub> = VDDS= 3.0 V, code 255	2.85		
	V <sub>REF</sub> = VDDS= 1.8 V, code 1	0.02		
Output voltage range	V <sub>REF</sub> = VDDS = 1.8 V, code 255	1.71		V
Load = Low Power Clocked Comparator	V <sub>REF</sub> = DCOUPL, pre-charge OFF, code 1	0.02		v
	V <sub>REF</sub> = DCOUPL, pre-charge OFF, code 255	1.20		
	V <sub>REF</sub> = DCOUPL, pre-charge ON, code 1	1.27		
	V <sub>REF</sub> = DCOUPL, pre-charge ON, code 255	2.46		
	V <sub>REF</sub> = ADCREF, code 1	0.02		
	V <sub>REF</sub> = ADCREF, code 255	1.42		

1 LSB (V<sub>REF</sub> 3.8 V/3.0 V/1.8 V/DCOUPL/ADCREF) = 14.10 mV/11.13 mV/6.68 mV/4.67 mV/5.48 mV (1)

(2) (3)

Includes comparator offset A load > 20 pF will increases the settling time

(4) Keysight 34401A Multimeter



## 7.15.3 Temperature and Battery Monitor

#### 7.15.3.1 Temperature Sensor

Measured on a Texas Instruments reference design with  $T_c$  = 25 °C,  $V_{DDS}$  = 3.0 V, unless otherwise noted.

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Resolution			2		°C
Accuracy	-40 °C to 0 °C		±4.0		°C
Accuracy	0 °C to 105 °C		±2.5		°C
Supply voltage coefficient <sup>(1)</sup>			3.6		°C/V

(1) The temperature sensor is automatically compensated for VDDS variation when using the TI-provided temperature driver.

#### 7.15.3.2 Battery Monitor

Measured on a Texas Instruments reference design with  $T_c$  = 25 °C, unless otherwise noted.

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Resolution			25		mV
Range		1.8		3.8	V
Integral nonlinearity (max)			23		mV
Accuracy	VDDS = 3.0 V		22.5		mV
Offset error			-32		mV
Gain error			-1		%

#### 7.15.4 Comparators

#### 7.15.4.1 Low-Power Clocked Comparator

 $T_c$  = 25 °C,  $V_{DDS}$  = 3.0 V, unless otherwise noted.

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Input voltage range		0		$V_{\text{DDS}}$	V
Clock frequency			SCLK_LF		
Internal reference voltage <sup>(1)</sup>	Using internal DAC with VDDS as reference voltage, DAC code = 0 - 255		0.024 - 2.865		V
Offset	Measured at V <sub>DDS</sub> / 2, includes error from internal DAC		±5		mV
Decision time	Step from –50 mV to 50 mV		1		Clock Cycle

(1) The comparator can use an internal 8 bits DAC as its reference. The DAC output voltage range depends on the reference voltage selected. See #none#

#### 7.15.4.2 Continuous Time Comparator

 $T_c = 25^{\circ}C$ ,  $V_{DDS} = 3.0$  V, unless otherwise noted.

PARAMETER	TEST CONDITIONS	MIN	TYP	MAX	UNIT
Input voltage range <sup>(1)</sup>		0		$V_{\text{DDS}}$	V
Offset	Measured at V <sub>DDS</sub> / 2		±5		mV
Decision time	Step from –10 mV to 10 mV		0.70		μs
Current consumption	Internal reference		8.0		μA

(1) The input voltages can be generated externally and connected throughout I/Os or an internal reference voltage can be generated using the DAC



# 7.15.5 Current Source

#### 7.15.5.1 Programmable Current Source

 $T_c$  = 25 °C,  $V_{DDS}$  = 3.0 V, unless otherwise noted.

PARAMETER	TEST CONDITIONS	MIN TYP	MAX	UNIT
Current source programmable output range (logarithmic range)		0.25 - 20		μA
Resolution		0.25		μA

#### 7.15.6 GPIO

#### 7.15.6.1 GPIO DC Characteristics

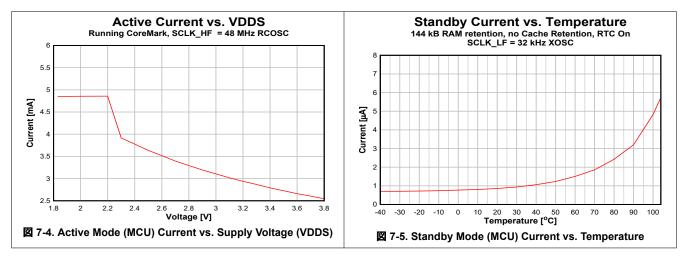
PARAMETER	TEST CONDITIONS	MIN TYP MAX	UNIT
T <sub>A</sub> = 25 °C, V <sub>DDS</sub> = 1.8 V		L	
GPIO VOH at 8 mA load	IOCURR = 2, high-drive GPIOs only	1.56	V
GPIO VOL at 8 mA load	IOCURR = 2, high-drive GPIOs only	0.24	V
GPIO VOH at 4 mA load	IOCURR = 1	1.59	V
GPIO VOL at 4 mA load	IOCURR = 1	0.21	V
GPIO pullup current	Input mode, pullup enabled, Vpad = 0 V	73	μA
GPIO pulldown current	Input mode, pulldown enabled, Vpad = VDDS	19	μA
GPIO low-to-high input transition, with hysteresis	IH = 1, transition voltage for input read as $0 \rightarrow 1$	1.08	V
GPIO high-to-low input transition, with hysteresis	IH = 1, transition voltage for input read as $1 \rightarrow 0$	0.73	V
GPIO input hysteresis	IH = 1, difference between $0 \rightarrow 1$ and $1 \rightarrow 0$ points	0.35	v
T <sub>A</sub> = 25 °C, V <sub>DDS</sub> = 3.0 V		1	1
GPIO VOH at 8 mA load	IOCURR = 2, high-drive GPIOs only	2.59	V
GPIO VOL at 8 mA load	IOCURR = 2, high-drive GPIOs only	0.42	V
GPIO VOH at 4 mA load	IOCURR = 1	2.63	V
GPIO VOL at 4 mA load	IOCURR = 1	0.40	V
T <sub>A</sub> = 25 °C, V <sub>DDS</sub> = 3.8 V			
GPIO pullup current	Input mode, pullup enabled, Vpad = 0 V	282	μA
GPIO pulldown current	Input mode, pulldown enabled, Vpad = VDDS	110	μA
GPIO low-to-high input transition, with hysteresis	IH = 1, transition voltage for input read as $0 \rightarrow 1$	1.97	V
GPIO high-to-low input transition, with hysteresis	IH = 1, transition voltage for input read as $1 \rightarrow 0$	1.55	V
GPIO input hysteresis	IH = 1, difference between $0 \rightarrow 1$ and $1 \rightarrow 0$ points	0.42	v
T <sub>A</sub> = 25 °C		1	1
VIH	Lowest GPIO input voltage reliably interpreted as a <i>High</i>	0.8*V <sub>DDS</sub>	v
VIL	Highest GPIO input voltage reliably interpreted as a Low	0.2*V <sub>DDS</sub>	v



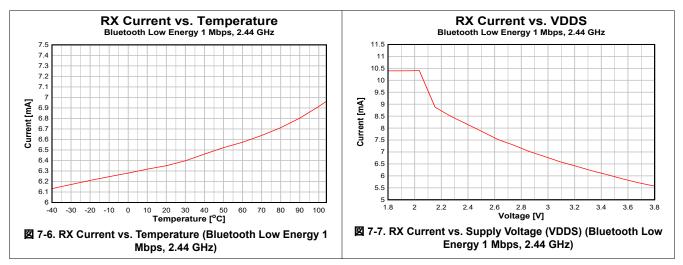
# 7.16 Typical Characteristics

All measurements in this section are done with  $T_c = 25$  °C and  $V_{DDS} = 3.0$  V, unless otherwise noted. See 22/2 = 22/7.3 for device limits. Values exceeding these limits are for reference only.

#### 7.16.1 MCU Current



#### 7.16.2 RX Current





#### 7.16.3 TX Current

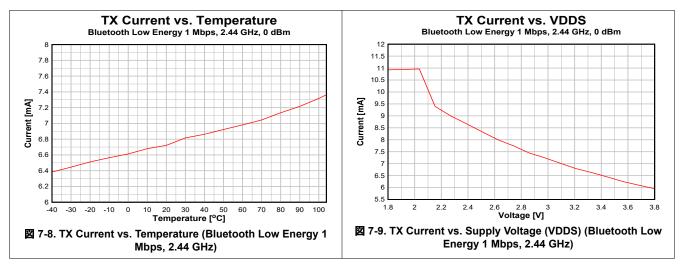


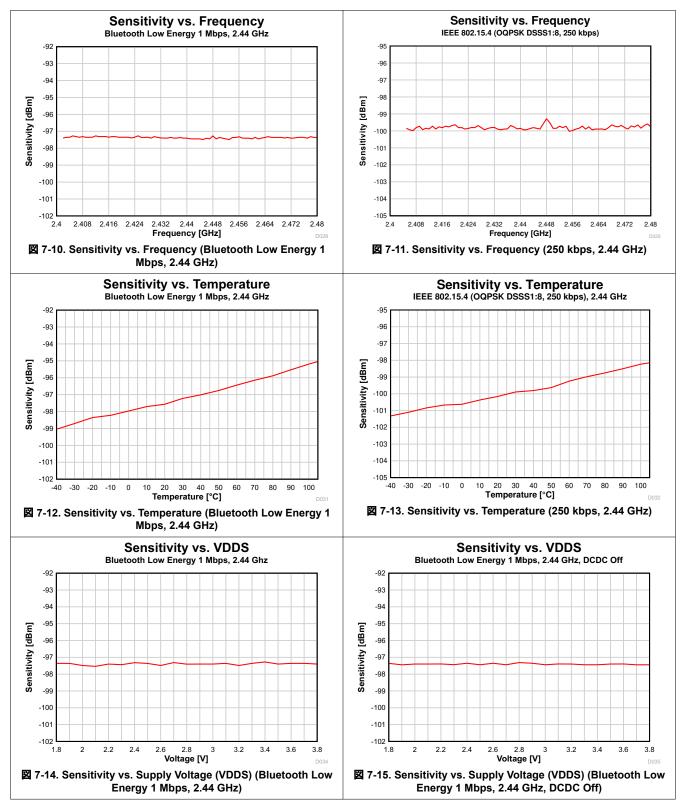
表 7-1.	. Typical TX Current and Output Power

CC2652R at 2.4 GHz, VDDS = $3.0 V^{(1)}$ (Measured on CC2652-R7EM-7ID)							
txPower	TX Power Setting (SmartRF Studio)	Typical Output Power [dBm]	Typical Current Consumption [mA]				
0x701F	5	4.8	10				
0x3A17	4	3.8	9				
0x3A64	3	2.7	8				
0x325F	2	1.7	8				
0x2C5C	1	1.0	8				
0x2659	0	0.1	7				
0x1697	-3	-2.8	7				
0x1693	-5	-4.8	6				
0x1292	-6	-5.4	6				
0x0CD3	-9	-8.9	5				
0x0AD1	-10	-10.2	5				
0x0ACF	-12	-11.8	5				
0x06CD	-15	-13.7	5				
0x06CA	-18	-16.9	5				
0x04C8	-20	-19.6	5				

(1) Internal regulated voltage powers the PA, therefore the output power is not affected by variation in VDDS voltage.

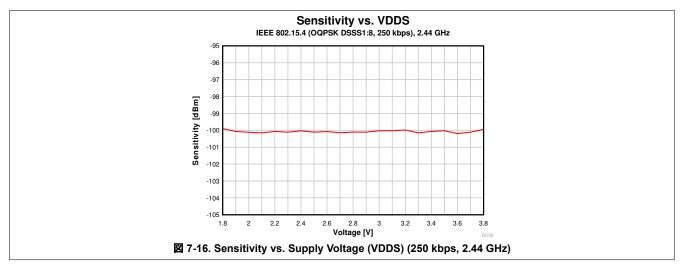


#### 7.16.4 RX Performance



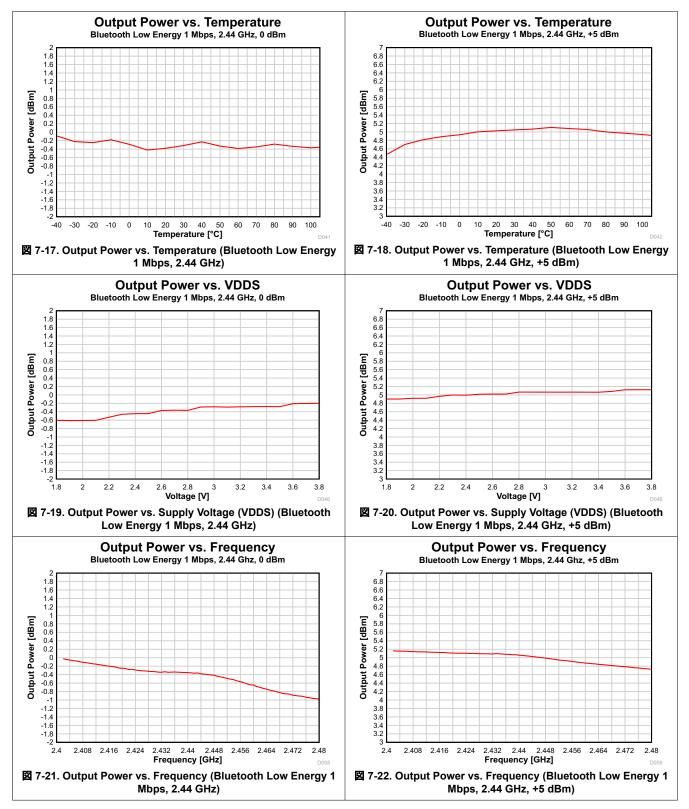


## 7.16.4 RX Performance (continued)



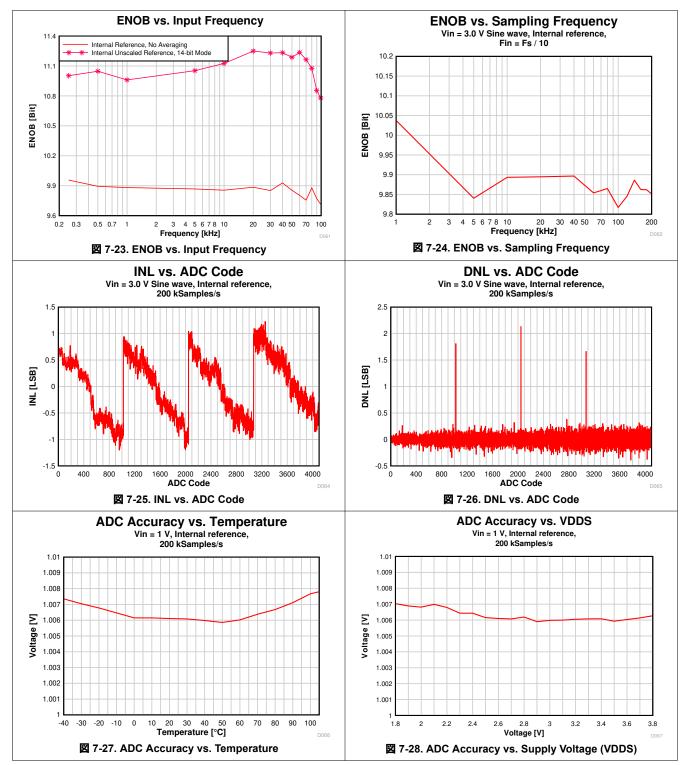


#### 7.16.5 TX Performance





## 7.16.6 ADC Performance





# 8 Detailed Description

# 8.1 Overview

セクション 3.1 shows the core modules of the CC2652R7 device.

# 8.2 System CPU

The CC2652R7 SimpleLink<sup>™</sup> Wireless MCU contains an Arm<sup>®</sup> Cortex<sup>®</sup>-M4F system CPU, which runs the application and the higher layers of radio protocol stacks.

The system CPU is the foundation of a high-performance, low-cost platform that meets the system requirements of minimal memory implementation, and low-power consumption, while delivering outstanding computational performance and exceptional system response to interrupts.

Its features include the following:

- · ARMv7-M architecture optimized for small-footprint embedded applications
- Arm Thumb<sup>®</sup>-2 mixed 16- and 32-bit instruction set delivers the high performance expected of a 32-bit Arm core in a compact memory size
- Fast code execution permits increased sleep mode time
- · Deterministic, high-performance interrupt handling for time-critical applications
- Single-cycle multiply instruction and hardware divide
- · Hardware division and fast digital-signal-processing oriented multiply accumulate
- Saturating arithmetic for signal processing
- IEEE 754-compliant single-precision Floating Point Unit (FPU)
- Memory Protection Unit (MPU) for safety-critical applications
- Full debug with data matching for watchpoint generation
  - Data Watchpoint and Trace Unit (DWT)
  - JTAG Debug Access Port (DAP)
  - Flash Patch and Breakpoint Unit (FPB)
  - Trace support reduces the number of pins required for debugging and tracing
  - Instrumentation Trace Macrocell Unit (ITM)
  - Trace Port Interface Unit (TPIU) with asynchronous serial wire output (SWO)
- Optimized for single-cycle flash memory access
- Tightly connected to 8-KB 4-way random replacement cache for minimal active power consumption and wait states
- Ultra-low-power consumption with integrated sleep modes
- 48 MHz operation
- 1.25 DMIPS per MHz



# 8.3 Radio (RF Core)

The RF Core is a highly flexible and future proof radio module which contains an Arm Cortex-M0 processor that interfaces the analog RF and base-band circuitry, handles data to and from the system CPU side, and assembles the information bits in a given packet structure. The RF core offers a high level, command-based API to the main CPU that configurations and data are passed through. The Arm Cortex-M0 processor is not programmable by customers and is interfaced through the TI-provided RF driver that is included with the SimpleLink Software Development Kit (SDK).

The RF core can autonomously handle the time-critical aspects of the radio protocols, thus offloading the main CPU, which reduces power and leaves more resources for the user application. Several signals are also available to control external circuitry such as RF switches or range extenders autonomously.

Multiprotocol solutions are enabled through time-sliced access of the radio, handled transparently for the application through the TI-provided RF driver and dual-mode manager.

The various physical layer radio formats are partly built as a software defined radio where the radio behavior is either defined by radio ROM contents or by non-ROM radio formats delivered in form of firmware patches with the SimpleLink SDKs. This allows the radio platform to be updated for support of future versions of standards even with over-the-air (OTA) updates while still using the same silicon.

#### 8.3.1 Bluetooth 5.2 Low Energy

The RF Core offers full support for Bluetooth 5.2 Low Energy, including the high-speed 2-Mbps physical layer and the 500-kbps and 125-kbps long range PHYs (Coded PHY) through the TI provided Bluetooth 5.2 stack or through a high-level Bluetooth API. The Bluetooth 5.2 PHY and part of the controller are in radio and system ROM, providing significant savings in memory usage and more space available for applications.

The new high-speed mode allows data transfers up to 2 Mbps, twice the speed of Bluetooth 4.2 and five times the speed of Bluetooth 4.0, without increasing power consumption. In addition to faster speeds, this mode offers significant improvements for energy efficiency and wireless coexistence with reduced radio communication time.

Bluetooth 5.2 also enables unparalleled flexibility for adjustment of speed and range based on application needs, which capitalizes on the high-speed or long-range modes respectively. Data transfers are now possible at 2 Mbps, enabling development of applications using voice, audio, imaging, and data logging that were not previously an option using Bluetooth Low Energy. With high-speed mode, existing applications deliver faster responses, richer engagement, and longer battery life. Bluetooth 5.2 enables fast, reliable firmware updates.

#### 8.3.2 802.15.4 (Thread, Zigbee, 6LoWPAN)

Through a dedicated IEEE radio API, the RF Core supports the 2.4-GHz IEEE 802.15.4-2011 physical layer (2 Mchips per second Offset-QPSK with DSSS 1:8), used in Thread, Zigbee, and 6LoWPAN protocols. The 802.15.4 PHY and MAC are in radio and system ROM. TI also provides royalty-free protocol stacks for Thread and Zigbee as part of the SimpleLink SDK, enabling a robust end-to-end solution.

#### 8.4 Memory

The up to 704KB nonvolatile (flash) memory provides storage for code and data. The flash memory is in-system programmable and erasable. The last flash memory sector must contain a Customer Configuration section (CCFG) that is used by boot ROM and TI provided drivers to configure the device. This configuration is done through the ccfg.c source file that is included in all TI provided examples.

The ultra-low leakage system static RAM (SRAM) is split into four 32KB and one 16KB blocks and can be used for both storage of data and execution of code. Retention of SRAM contents in Standby power mode is enabled by default and included in Standby mode power consumption numbers. Parity checking for detection of bit errors in memory is built-in, which reduces chip-level soft errors and thereby increases reliability. System SRAM is always initialized to zeroes upon code execution from boot.

To improve code execution speed and lower power when executing code from nonvolatile memory, a 4-way nonassociative 8-KB cache is enabled by default to cache and prefetch instructions read by the system CPU.



The cache can be used as a general-purpose RAM by enabling this feature in the Customer Configuration Area (CCFG).

There is a 4KB ultra-low leakage SRAM available for use with the Sensor Controller Engine which is typically used for storing Sensor Controller programs, data and configuration parameters. This RAM is also accessible by the system CPU. The Sensor Controller RAM is not cleared to zeroes between system resets.

The ROM includes a TI-RTOS kernel and low-level drivers, as well as significant parts of selected radio stacks, which frees up flash memory for the application. The ROM also contains a serial (SPI and UART) bootloader that can be used for initial programming of the device.

#### 8.5 Sensor Controller

The Sensor Controller contains circuitry that can be selectively enabled in both Standby and Active power modes. The peripherals in this domain can be controlled by the Sensor Controller Engine, which is a proprietary power-optimized CPU. This CPU can read and monitor sensors or perform other tasks autonomously; thereby significantly reducing power consumption and offloading the system CPU.

The Sensor Controller Engine is user programmable with a simple programming language that has syntax similar to C. This programmability allows for sensor polling and other tasks to be specified as sequential algorithms rather than static configuration of complex peripheral modules, timers, DMA, register programmable state machines, or event routing.

The main advantages are:

- Flexibility data can be read and processed in unlimited manners while still ensuring ultra-low power
- 2 MHz low-power mode enables lowest possible handling of digital sensors
- Dynamic reuse of hardware resources
- · 40-bit accumulator supporting multiplication, addition and shift
- Observability and debugging options

Sensor Controller Studio is used to write, test, and debug code for the Sensor Controller. The tool produces C driver source code, which the System CPU application uses to control and exchange data with the Sensor Controller. Typical use cases may be (but are not limited to) the following:

- Read analog sensors using integrated ADC or comparators
- Interface digital sensors using GPIOs, SPI, UART, or I<sup>2</sup>C (UART and I<sup>2</sup>C are bit-banged)
- · Capacitive sensing
- Waveform generation
- Very low-power pulse counting (flow metering)
- Key scan

The peripherals in the Sensor Controller include the following:

- The low-power clocked comparator can be used to wake the system CPU from any state in which the comparator is active. A configurable internal reference DAC can be used in conjunction with the comparator. The output of the comparator can also be used to trigger an interrupt or the ADC.
- Capacitive sensing functionality is implemented through the use of a constant current source, a time-to-digital converter, and a comparator. The continuous time comparator in this block can also be used as a higheraccuracy alternative to the low-power clocked comparator. The Sensor Controller takes care of baseline tracking, hysteresis, filtering, and other related functions when these modules are used for capacitive sensing.
- The ADC is a 12-bit, 200-ksamples/s ADC with eight inputs and a built-in voltage reference. The ADC can be triggered by many different sources including timers, I/O pins, software, and comparators.
- · The analog modules can connect to up to eight different GPIOs
- Dedicated SPI master with up to 6 MHz clock speed

The peripherals in the Sensor Controller can also be controlled from the main application processor.



### 8.6 Cryptography

The CC2652R7 device comes with a wide set of modern cryptography-related hardware accelerators, drastically reducing code footprint and execution time for cryptographic operations. It also has the benefit of being lower power and improves availability and responsiveness of the system because the cryptography operations runs in a background hardware thread.

Together with a large selection of open-source cryptography libraries provided with the Software Development Kit (SDK), this allows for secure and future proof IoT applications to be easily built on top of the platform. The hardware accelerator modules are:

- **True Random Number Generator (TRNG)** module provides a true, nondeterministic noise source for the purpose of generating keys, initialization vectors (IVs), and other random number requirements. The TRNG is built on 24 ring oscillators that create unpredictable output to feed a complex nonlinear-combinatorial circuit.
- Secure Hash Algorithm 2 (SHA-2) with support for SHA224, SHA256, SHA384, and SHA512
- Advanced Encryption Standard (AES) with 128 and 256 bit key lengths
- **Public Key Accelerator** Hardware accelerator supporting mathematical operations needed for elliptic curves up to 512 bits and RSA key pair generation up to 1024 bits.

Through use of these modules and the TI provided cryptography drivers, the following capabilities are available for an application or stack:

- Key Agreement Schemes
  - Elliptic curve Diffie–Hellman with static or ephemeral keys (ECDH and ECDHE)
  - Elliptic curve Password Authenticated Key Exchange by Juggling (ECJ-PAKE)
- Signature Generation
  - Elliptic curve Diffie-Hellman Digital Signature Algorithm (ECDSA)
- Curve Support
  - Short Weierstrass form (full hardware support), such as:
    - NIST-P224, NIST-P256, NIST-P384, NIST-P521
    - Brainpool-256R1, Brainpool-384R1, Brainpool-512R1
    - secp256r1
  - Montgomery form (hardware support for multiplication), such as:
    - Curve25519
- SHA2 based MACs
  - HMAC with SHA224, SHA256, SHA384, or SHA512
  - Block cipher mode of operation
  - AESCCM
  - AESGCM
  - AESECB
  - AESCBC
  - AESCBC-MAC
- True random number generation

Other capabilities, such as RSA encryption and signatures as well as Edwards type of elliptic curves such as Curve1174 or Ed25519, can also be implemented using the provided hardware accelerators but are not part of the TI SimpleLink SDK for the CC2652R7 device.



### 8.7 Timers

A large selection of timers are available as part of the CC2652R7 device. These timers are:

#### • Real-Time Clock (RTC)

A 70-bit 3-channel timer running on the 32 kHz low frequency system clock (SCLK\_LF). This timer is available in all power modes except Shutdown. The timer can be calibrated to compensate for frequency drift when using the RCOSC\_LF as the low frequency system clock. If an external LF clock with frequency different from 32.768 kHz is used, the RTC tick speed can be adjusted to compensate for this. When using TI-RTOS, the RTC is used as the base timer in the operating system and should thus only be accessed through the kernel APIs such as the Clock module. The real time clock can also be read by the Sensor Controller Engine to timestamp sensor data and also has dedicated capture channels. By default, the RTC halts when a debugger halts the device.

#### • General Purpose Timers (GPTIMER)

The four flexible GPTIMERs can be used as either 4× 32 bit timers or 8× 16 bit timers, all running on up to 48 MHz. Each of the 16- or 32-bit timers support a wide range of features such as one-shot or periodic counting, pulse width modulation (PWM), time counting between edges and edge counting. The inputs and outputs of the timer are connected to the device event fabric, which allows the timers to interact with signals such as GPIO inputs, other timers, DMA and ADC. The GPTIMERs are available in Active and Idle power modes.

#### Sensor Controller Timers

The Sensor Controller contains 3 timers:

AUX Timer 0 and 1 are 16-bit timers with a 2<sup>N</sup> prescaler. Timers can either increment on a clock or on each edge of a selected tick source. Both one-shot and periodical timer modes are available.

AUX Timer 2 is a 16-bit timer that can operate at 24 MHz, 2 MHz or 32 kHz independent of the Sensor Controller functionality. There are 4 capture or compare channels, which can be operated in one-shot or periodical modes. The timer can be used to generate events for the Sensor Controller Engine or the ADC, as well as for PWM output or waveform generation.

#### Radio Timer

A multichannel 32-bit timer running at 4 MHz is available as part of the device radio. The radio timer is typically used as the timing base in wireless network communication using the 32-bit timing word as the network time. The radio timer is synchronized with the RTC by using a dedicated radio API when the device radio is turned on or off. This ensures that for a network stack, the radio timer seems to always be running when the radio is enabled. The radio timer is in most cases used indirectly through the trigger time fields in the radio APIs and should only be used when the accurate 48 MHz high frequency crystal is the source of SCLK\_HF.

#### Watchdog timer

The watchdog timer is used to regain control if the system operates incorrectly due to software errors. It is typically used to generate an interrupt to and reset of the device for the case where periodic monitoring of the system components and tasks fails to verify proper functionality. The watchdog timer runs on a 1.5 MHz clock rate and cannot be stopped once enabled. The watchdog timer pauses to run in Standby power mode and when a debugger halts the device.



#### 8.8 Serial Peripherals and I/O

The SSIs are synchronous serial interfaces that are compatible with SPI, MICROWIRE, and TI's synchronous serial interfaces. The SSIs support both SPI master and slave up to 4 MHz. The SSI modules support configurable phase and polarity.

The UARTs implement universal asynchronous receiver and transmitter functions. They support flexible baudrate generation up to a maximum of 3 Mbps.

The I<sup>2</sup>S interface is used to handle digital audio and can also be used to interface pulse-density modulation microphones (PDM).

The  $I^2C$  interface is used to communicate with devices compatible with the  $I^2C$  standard. The  $I^2C$  interface can handle 100 kHz and 400 kHz operation, and can serve as both master and slave.

The I/O controller (IOC) controls the digital I/O pins and contains multiplexer circuitry to allow a set of peripherals to be assigned to I/O pins in a flexible manner. All digital I/Os are interrupt and wake-up capable, have a programmable pullup and pulldown function, and can generate an interrupt on a negative or positive edge (configurable). When configured as an output, pins can function as either push-pull or open-drain. Five GPIOs have high-drive capabilities, which are marked in **bold** in  $\forall 2 \neq 2 \Rightarrow 0$ . All digital peripherals can be connected to any digital pin on the device.

For more information, see the CC13x2x7, CC26x2x7 SimpleLink<sup>™</sup> Wireless MCU Technical Reference Manual.

#### 8.9 Battery and Temperature Monitor

A combined temperature and battery voltage monitor is available in the CC2652R7 device. The battery and temperature monitor allows an application to continuously monitor on-chip temperature and supply voltage and respond to changes in environmental conditions as needed. The module contains window comparators to interrupt the system CPU when temperature or supply voltage go outside defined windows. These events can also be used to wake up the device from Standby mode through the Always-On (AON) event fabric.

#### 8.10 µDMA

The device includes a direct memory access ( $\mu$ DMA) controller. The  $\mu$ DMA controller provides a way to offload data-transfer tasks from the system CPU, thus allowing for more efficient use of the processor and the available bus bandwidth. The  $\mu$ DMA controller can perform a transfer between memory and peripherals. The  $\mu$ DMA controller has dedicated channels for each supported on-chip module and can be programmed to automatically perform transfers between peripherals and memory when the peripheral is ready to transfer more data.

Some features of the µDMA controller include the following (this is not an exhaustive list):

- · Highly flexible and configurable channel operation of up to 32 channels
- Transfer modes: memory-to-memory, memory-to-peripheral, peripheral-to-memory, and peripheral-to-peripheral
- Data sizes of 8, 16, and 32 bits
- Ping-pong mode for continuous streaming of data

#### 8.11 Debug

The on-chip debug support is done through a dedicated cJTAG (IEEE 1149.7) or JTAG (IEEE 1149.1) interface. The device boots by default into cJTAG mode and must be reconfigured to use 4-pin JTAG.



#### 8.12 Power Management

To minimize power consumption, the CC2652R7 supports a number of power modes and power management features (see  $\frac{1}{5}$  8-1).

表 8-1. Power Modes									
MODE	SOFT	RESET PIN							
MODE	ACTIVE	IDLE	STANDBY	SHUTDOWN	HELD				
CPU	Active	Off	Off	Off	Off				
Flash	On	Available	Off	Off	Off				
SRAM	On	On	Retention	Off	Off				
Supply System	On	On	Duty Cycled	Off	Off				
Register and CPU retention	Full	Full	Partial	No	No				
SRAM retention	Full	Full	Full	No	No				
48 MHz high-speed clock (SCLK_HF)	XOSC_HF or RCOSC_HF	XOSC_HF or RCOSC_HF	Off	Off	Off				
2 MHz medium-speed clock (SCLK_MF)	RCOSC_MF	RCOSC_MF	Available	Off	Off				
32 kHz low-speed clock (SCLK_LF)	XOSC_LF or RCOSC_LF	XOSC_LF or RCOSC_LF	XOSC_LF or RCOSC_LF	Off	Off				
Peripherals	Available	Available	Off	Off	Off				
Sensor Controller	Available	Available	Available	Off	Off				
Wake-up on RTC	Available	Available	Available	Off	Off				
Wake-up on pin edge	Available	Available	Available	Available	Off				
Wake-up on reset pin	On	On	On	On	On				
Brownout detector (BOD)	On	On	Duty Cycled	Off	Off				
Power-on reset (POR)	On	On	On	Off	Off				
Watchdog timer (WDT)	Available	Available	Paused	Off	Off				

In **Active** mode, the application system CPU is actively executing code. Active mode provides normal operation of the processor and all of the peripherals that are currently enabled. The system clock can be any available clock source (see  $\ge 8-1$ ).

In **Idle** mode, all active peripherals can be clocked, but the Application CPU core and memory are not clocked and no code is executed. Any interrupt event brings the processor back into active mode.

In **Standby** mode, only the always-on (AON) domain is active. An external wake-up event, RTC event, or Sensor Controller event is required to bring the device back to active mode. MCU peripherals with retention do not need to be reconfigured when waking up again, and the CPU continues execution from where it went into standby mode. All GPIOs are latched in standby mode.

In **Shutdown** mode, the device is entirely turned off (including the AON domain and Sensor Controller), and the I/Os are latched with the value they had before entering shutdown mode. A change of state on any I/O pin defined as a *wake from shutdown pin* wakes up the device and functions as a reset trigger. The CPU can differentiate between reset in this way and reset-by-reset pin or power-on reset by reading the reset status register. The only state retained in this mode is the latched I/O state and the flash memory contents.



The Sensor Controller is an autonomous processor that can control the peripherals in the Sensor Controller independently of the system CPU. This means that the system CPU does not have to wake up, for example to perform an ADC sampling or poll a digital sensor over SPI, thus saving both current and wake-up time that would otherwise be wasted. The Sensor Controller Studio tool enables the user to program the Sensor Controller, control its peripherals, and wake up the system CPU as needed. All Sensor Controller peripherals can also be controlled by the system CPU.

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The power, RF and clock management for the CC2652R7 device require specific configuration and handling by software for optimized performance. This configuration and handling is implemented in the TI-provided drivers that are part of the SimpleLink<sup>™</sup> CC13xx and CC26xx software development kit (SDK). Therefore, TI highly recommends using this software framework for all application development on the device. The complete SDK with TI-RTOS (optional), device drivers, and examples are offered free of charge in source code.

#### 8.13 Clock Systems

The CC2652R7 device has several internal system clocks.

The 48 MHz SCLK\_HF is used as the main system (MCU and peripherals) clock. This can be driven by the internal 48 MHz RC Oscillator (RCOSC\_HF) or an external 48 MHz crystal (XOSC\_HF). Radio operation requires an external 48 MHz crystal.

SCLK\_MF is an internal 2 MHz clock that is used by the Sensor Controller in low-power mode and also for internal power management circuitry. The SCLK\_MF clock is always driven by the internal 2 MHz RC Oscillator (RCOSC\_MF).

SCLK\_LF is the 32.768 kHz internal low-frequency system clock. It can be used by the Sensor Controller for ultra-low-power operation and is also used for the RTC and to synchronize the radio timer before or after Standby power mode. SCLK\_LF can be driven by the internal 32.8 kHz RC Oscillator (RCOSC\_LF), a 32.768 kHz watch-type crystal, or a clock input on any digital IO.

When using a crystal or the internal RC oscillator, the device can output the 32 kHz SCLK\_LF signal to other devices, thereby reducing the overall system cost.

#### 8.14 Network Processor

Depending on the product configuration, the CC2652R7 device can function as a wireless network processor (WNP - a device running the wireless protocol stack with the application running on a separate host MCU), or as a system-on-chip (SoC) with the application and protocol stack running on the device's system CPU inside the device.

In the first case, the external host MCU communicates with the device using SPI or UART. In the second case, the application must be written according to the application framework supplied with the wireless protocol stack.



### 9 Application, Implementation, and Layout

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Information in the following Applications section is not part of the TI component specification, and TI does not warrant its accuracy or completeness. TI's customers are responsible for determining suitability of components for their purposes. Customers should validate and test their design implementation to confirm system functionality.

For general design guidelines and hardware configuration guidelines, refer to CC13xx/CC26xx Hardware Configuration and PCB Design Considerations Application Report.

#### 9.1 Reference Designs

The following reference designs should be followed closely when implementing designs using the CC2652R7 device.

Special attention must be paid to RF component placement, decoupling capacitors and DCDC regulator components, as well as ground connections for all of these.

CC26x2-R7EM-7ID Design Files	The differential CC26x2-R7EM-7ID reference design provides schematic, layout and production files for the characterization board used for deriving the performance number found in this document.
LP-CC2652R7 Design Files	The CC26X2R LaunchPad Design Files contain detailed schematics and layouts to build application specific boards using the CC2652R7 device. This design applies to both the CC2642R and CC2652R devices.
Sub-1 GHz and 2.4 GHz Antenna K for LaunchPad™ Development Kit and SensorTag	<ul> <li>The antenna kit allows real-life testing to identify the optimal antenna for your</li> <li>application. The antenna kit includes 16 antennas for frequencies from 169 MHz to 2.4 GHz, including:</li> <li>PCB antennas</li> <li>Helical antennas</li> <li>Chip antennas</li> <li>Dual-band antennas for 868 MHz and 915 MHz combined with 2.4 GHz</li> </ul>
	The antenna kit includes a ISC cable to connect to the Wireless MCUL aunchPad

The antenna kit includes a JSC cable to connect to the Wireless MCU LaunchPad Development Kits and SensorTags.

#### **9.2 Junction Temperature Calculation**

This section shows the different techniques for calculating the junction temperature under various operating conditions. For more details, see *Semiconductor and IC Package Thermal Metrics*.

There are three recommended ways to derive the junction temperature from other measured temperatures:

1. From package temperature:

$T_J = \psi_{\rm JT} \times P + T_{\rm case}$	(1)
From board temperature:	
$T_J = \psi_{\rm JB} \times P + T_{\rm board}$	(2)
From ambient temperature:	
$T_J = R_{\Theta JA} \times P + T_A$	(3)

P is the power dissipated from the device and can be calculated by multiplying current consumption with supply voltage. Thermal resistance coefficients are found in  $\frac{1}{2}\sqrt{2} \frac{1}{2}\sqrt{7.8}$ .

Example:

2.

3.

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(4)

Using  $\overrightarrow{x}$  3, the temperature difference between ambient temperature and junction temperature is calculated. In this example, we assume a simple use case where the radio is transmitting continuously at 0dBm output power. Let us assume the ambient temperature is 105 °C and the supply voltage is 3.0 V. To calculate P, we need to look up the current consumption for Tx at 105 °C in  $\boxed{2}$  7-8. From the plot, we see that the current consumption is 8.1 mA. This means that P is 3.0 V × 8.1 mA = 194.4 mW.

The junction temperature is then calculated as:

$$T_J = 23.4^{\circ}C/W \times 194.4mW + T_A = 4.5^{\circ}C + T_A$$

As can be seen from the example, the junction temperature is 4.5 °C higher than the ambient temperature when running continuous Tx at 105 °C and, thus, well within the recommended operating conditions of 115 °C.

For various application use cases current consumption for other modules may have to be added to calculate the appropriate power dissipation. For example, the MCU may be running simultaneously as the radio, peripheral modules may be enabled, etc. Typically, the easiest way to find the peak current consumption, and thus the peak power dissipation in the device, is to measure as described in *Measuring CC13xx and CC26xx Current Consumption*.



### **10 Device and Documentation Support**

TI offers an extensive line of development tools. Tools and software to evaluate the performance of the device, generate code, and develop solutions are listed as follows.

#### **10.1 Device Nomenclature**

To designate the stages in the product development cycle, TI assigns prefixes to all part numbers and/or datecode. Each device has one of three prefixes/identifications: X, P, or null (no prefix) (for example, XCC2652R7 is in preview; therefore, an X prefix/identification is assigned).

Device development evolutionary flow:

- **X** Experimental device that is not necessarily representative of the final device's electrical specifications and may not use production assembly flow.
- **P** Prototype device that is not necessarily the final silicon die and may not necessarily meet final electrical specifications.

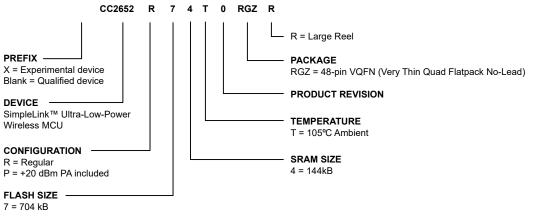
null Production version of the silicon die that is fully qualified.

Production devices have been characterized fully, and the quality and reliability of the device have been demonstrated fully. TI's standard warranty applies.

Predictions show that prototype devices (X or P) have a greater failure rate than the standard production devices. Texas Instruments recommends that these devices not be used in any production system because their expected end-use failure rate still is undefined. Only qualified production devices are to be used.

TI device nomenclature also includes a suffix with the device family name. This suffix indicates the package type (for example, *RGZ*).

For orderable part numbers of *CC2652R7* devices in the RGZ (7-mm x 7-mm) package type, see the *Package Option Addendum* of this document, the Device Information in セクション 3, the TI website (www.ti.com), or contact your TI sales representative.



**10-1.** Device Nomenclature

#### 10.2 Tools and Software

The CC2652R7 device is supported by a variety of software and hardware development tools.

#### **Development Kit**

CC2652R7 LaunchPad<sup>™</sup> Development Kit Development Kit SimpleLink Wireless MCU, which allows you to quickly evaluate and prototype 2.4-GHz

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wireless applications such as Bluetooth 5 Low Energy, Zigbee and Thread, plus combinations of these. The kit works with the LaunchPad ecosystem, easily enabling additional functionality like sensors, display and more. The built-in EnergyTrace<sup>™</sup> software is an energy-based code analysis tool that measures and displays the application's energy profile and helps to optimize it for ultra-low-power consumption. See  $\gtrsim 5-1$  for guidance in selecting the correct device for single-protocol products.

#### Software

#### SimpleLink™ CC13XX-CC26XX SDK

The SimpleLink CC13xx and CC26xx Software Development Kit (SDK) provides a complete package for the development of wireless applications on the CC13XX / CC26XX family of devices. The SDK includes a comprehensive software package for the CC2652R7 device, including the following protocol stacks:

- Bluetooth Low Energy 4 and 5.2
- Thread (based on OpenThread)
- Zigbee 3.0
- Wi-SUN®
- TI 15.4-Stack an IEEE 802.15.4-based star networking solution for Sub-1 GHz and 2.4 GHz
- Proprietary RF a large set of building blocks for building proprietary RF software
- Multiprotocol support concurrent operation between stacks using the Dynamic Multiprotocol Manager (DMM)

The SimpleLink CC13XX-CC26XX SDK is part of TI's SimpleLink MCU platform, offering a single development environment that delivers flexible hardware, software and tool options for customers developing wired and wireless applications. For more information about the SimpleLink MCU Platform, visit http://www.ti.com/simplelink.



#### **Development Tools**

•	
Code Composer Studio <sup>™</sup> Integrated Development Environment (IDE	Code Composer Studio is an integrated development environment (IDE) that supports TI's Microcontroller and Embedded Processors portfolio. Code Composer Studio comprises a suite of tools used to develop and debug embedded applications. It includes an optimizing C/C++ compiler, source code editor, project build environment, debugger, profiler, and many other features. The intuitive IDE provides a single user interface taking you through each step of the application development flow. Familiar tools and interfaces allow users to get started faster than ever before. Code Composer Studio combines the advantages of the Eclipse <sup>®</sup> software framework with advanced embedded debug capabilities from TI resulting in a compelling feature-rich development environment for embedded developers.
	CCS has support for all SimpleLink Wireless MCUs and includes support for EnergyTrace <sup>™</sup> software (application energy usage profiling). A real-time object viewer plugin is available for TI-RTOS, part of the SimpleLink SDK.
	Code Composer Studio is provided free of charge when used in conjunction with the XDS debuggers included on a LaunchPad Development Kit.
Code Composer Studio™ Cloud IDE	Code Composer Studio (CCS) Cloud is a web-based IDE that allows you to create, edit and build CCS and Energia <sup>™</sup> projects. After you have successfully built your project, you can download and run on your connected LaunchPad. Basic debugging, including features like setting breakpoints and viewing variable values is now supported with CCS Cloud.
IAR Embedded Workbench <sup>®</sup> for Arm <sup>®</sup>	IAR Embedded Workbench <sup>®</sup> is a set of development tools for building and debugging embedded system applications using assembler, C and C++. It provides a completely integrated development environment that includes a project manager, editor, and build tools. IAR has support for all SimpleLink Wireless MCUs. It offers broad debugger support, including XDS110, IAR I-jet <sup>™</sup> and Segger J-Link <sup>™</sup> . A real-time object viewer plugin is available for TI-RTOS, part of the SimpleLink SDK. IAR is also supported out-of-the-box on most software examples provided as part of the SimpleLink SDK.
	A 30-day evaluation or a 32 KB size-limited version is available through iar.com.
SmartRF™ Studio	SimpleLink Wireless MCUs from Texas Instruments. The application will help designers of RF systems to easily evaluate the radio at an early stage in the design process. It is especially useful for generation of configuration register values and for practical testing and debugging of the RF system. SmartRF Studio can be used either as a standalone application or together with applicable evaluation boards or debug probes for the RF device. Features of the SmartRF Studio include: • Link tests - transmit and receive packets between nodes
	<ul> <li>Antenna and radiation tests - set the radio in continuous wave TX and RX states</li> <li>Export radio configuration code for use with the TI SimpleLink SDK RF driver</li> <li>Custom GPIO configuration for signaling and control of external switches</li> </ul>
Sensor Controller Studio	Sensor Controller Studio is used to write, test and debug code for the Sensor Controller peripheral. The tool generates a Sensor Controller Interface driver, which is a set of C source files that are compiled into the System CPU application. These source files also contain the Sensor Controller binary image and allow the System CPU application to control and exchange data with the Sensor Controller. Features of the Sensor Controller Studio include: • Ready-to-use examples for several common use cases
	<ul> <li>Full toolchain with built-in compiler and assembler for programming in a C-like</li> </ul>

• Full toolchain with built-in compiler and assembler for programming in a C-like programming language



- Provides rapid development by using the integrated sensor controller task testing and debugging functionality, including visualization of sensor data and verification of algorithms
- CCS UniFlash CCS UniFlash is a standalone tool used to program on-chip flash memory on TI MCUs. UniFlash has a GUI, command line, and scripting interface. CCS UniFlash is available free of charge.

#### 10.2.1 SimpleLink<sup>™</sup> Microcontroller Platform

The SimpleLink microcontroller platform sets a new standard for developers with the broadest portfolio of wired and wireless Arm<sup>®</sup> MCUs (System-on-Chip) in a single software development environment. Delivering flexible hardware, software and tool options for your IoT applications. Invest once in the SimpleLink software development kit and use throughout your entire portfolio. Learn more on ti.com/simplelink.

#### **10.3 Documentation Support**

To receive notification of documentation updates on data sheets, errata, application notes and similar, navigate to the device product folder on ti.com/product/CC2652R7. In the upper right corner, click on *Alert me* to register and receive a weekly digest of any product information that has changed. For change details, review the revision history included in any revised document.

The current documentation that describes the MCU, related peripherals, and other technical collateral is listed as follows.

#### **TI Resource Explorer**

TI Resource Explorer Software examples, libraries, executables, and documentation are available for your device and development board.

#### Errata

*CC2652R7 Silicon Errata* The silicon errata describes the known exceptions to the functional specifications for each silicon revision of the device and description on how to recognize a device revision.

#### **Application Reports**

All application reports for the CC2652R7 device are found on the device product folder at: ti.com/product/ CC2652R7/#tech-docs.

#### **Technical Reference Manual (TRM)**

CC13x2x7, CC26x2x7 SimpleLink™	The TRM provides a detailed description of all modules and
Wireless MCU TRM	peripherals available in the device family.

### 10.4 サポート・リソース

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#### 10.7 用語集

テキサス・インスツルメンツ用語集

この用語集には、用語や略語の一覧および定義が記載されています。



## 11 Mechanical, Packaging, and Orderable Information



### PACKAGING INFORMATION

Orderable Device	Status (1)	Package Type	Package Drawing	Pins	Package Qty	Eco Plan (2)	Lead finish/ Ball material	MSL Peak Temp (3)	Op Temp (°C)	Device Marking (4/5)	Samples
CC2652R74T0RGZR	ACTIVE	VQFN	RGZ	48	2500	RoHS & Green	NIPDAU	Level-3-260C-168 HR	-40 to 105	CC2652 R74	Samples

<sup>(1)</sup> The marketing status values are defined as follows:

ACTIVE: Product device recommended for new designs.

LIFEBUY: TI has announced that the device will be discontinued, and a lifetime-buy period is in effect.

NRND: Not recommended for new designs. Device is in production to support existing customers, but TI does not recommend using this part in a new design.

**PREVIEW:** Device has been announced but is not in production. Samples may or may not be available.

**OBSOLETE:** TI has discontinued the production of the device.

<sup>(2)</sup> RoHS: TI defines "RoHS" to mean semiconductor products that are compliant with the current EU RoHS requirements for all 10 RoHS substances, including the requirement that RoHS substance do not exceed 0.1% by weight in homogeneous materials. Where designed to be soldered at high temperatures, "RoHS" products are suitable for use in specified lead-free processes. TI may reference these types of products as "Pb-Free".

**RoHS Exempt:** TI defines "RoHS Exempt" to mean products that contain lead but are compliant with EU RoHS pursuant to a specific EU RoHS exemption.

Green: TI defines "Green" to mean the content of Chlorine (CI) and Bromine (Br) based flame retardants meet JS709B low halogen requirements of <=1000ppm threshold. Antimony trioxide based flame retardants must also meet the <=1000ppm threshold requirement.

<sup>(3)</sup> MSL, Peak Temp. - The Moisture Sensitivity Level rating according to the JEDEC industry standard classifications, and peak solder temperature.

<sup>(4)</sup> There may be additional marking, which relates to the logo, the lot trace code information, or the environmental category on the device.

<sup>(5)</sup> Multiple Device Markings will be inside parentheses. Only one Device Marking contained in parentheses and separated by a "~" will appear on a device. If a line is indented then it is a continuation of the previous line and the two combined represent the entire Device Marking for that device.

<sup>(6)</sup> Lead finish/Ball material - Orderable Devices may have multiple material finish options. Finish options are separated by a vertical ruled line. Lead finish/Ball material values may wrap to two lines if the finish value exceeds the maximum column width.

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### TAPE AND REEL INFORMATION





#### QUADRANT ASSIGNMENTS FOR PIN 1 ORIENTATION IN TAPE



*All dimensions are nominal												
Device		Package Drawing		SPQ	Reel Diameter (mm)	Reel Width W1 (mm)	· · /	B0 (mm)	K0 (mm)	P1 (mm)	W (mm)	Pin1 Quadrant
CC2652R74T0RGZR	VQFN	RGZ	48	2500	330.0	16.4	7.3	7.3	1.1	12.0	16.0	Q2



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# PACKAGE MATERIALS INFORMATION

15-Jun-2023



\*All dimensions are nominal

Device	Package Type	Package Drawing	Pins	SPQ	Length (mm)	Width (mm)	Height (mm)
CC2652R74T0RGZR	VQFN	RGZ	48	2500	367.0	367.0	35.0

# **RGZ 48**

7 x 7, 0.5 mm pitch

# **GENERIC PACKAGE VIEW**

## VQFN - 1 mm max height

PLASTIC QUADFLAT PACK- NO LEAD



Images above are just a representation of the package family, actual package may vary. Refer to the product data sheet for package details.

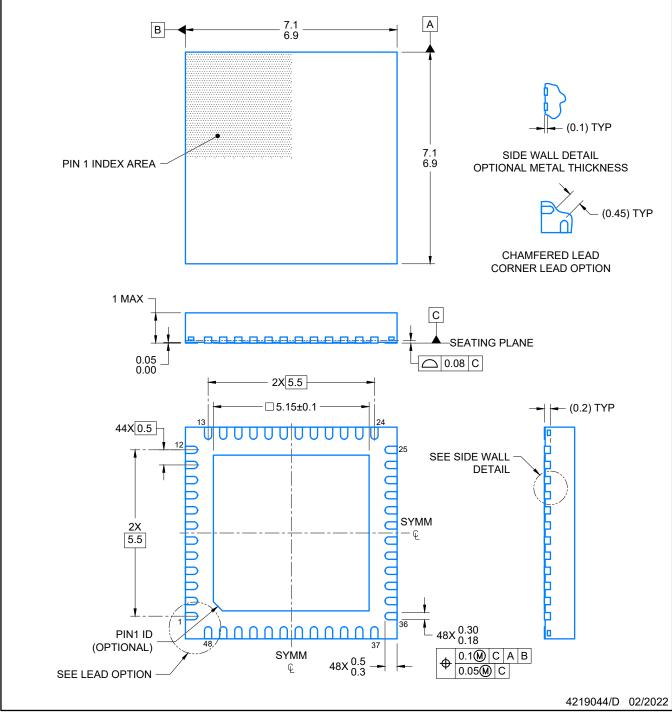


# **RGZ0048A**

# PACKAGE OUTLINE VQFN - 1 mm max height

VQI II IIIIII IIIAX Holgiii

PLASTIC QUADFLAT PACK- NO LEAD



#### NOTES:

- 1. All linear dimensions are in millimeters. Any dimensions in parenthesis are for reference only. Dimensioning and tolerancing per ASME Y14.5M.
- 2. This drawing is subject to change without notice.
- 3. The package thermal pad must be soldered to the printed circuit board for optimal thermal and mechanical performance.



# **EXAMPLE BOARD LAYOUT**

### VQFN - 1 mm max height

PLASTIC QUADFLAT PACK- NO LEAD



NOTES: (continued)

- 4. This package is designed to be soldered to a thermal pad on the board. For more information, see Texas Instruments literature number SLUA271 (www.ti.com/lit/slua271).
- 5. Vias are optional depending on application, refer to device data sheet. If any vias are implemented, refer to their locations shown on this view. It is recommended that vias under paste be filled, plugged or tented.



# **RGZ0048A**

# **RGZ0048A**

# **EXAMPLE STENCIL DESIGN**

# VQFN - 1 mm max height

PLASTIC QUADFLAT PACK- NO LEAD



6. Laser cutting apertures with trapezoidal walls and rounded corners may offer better paste release. IPC-7525 may have alternate design recommendations.



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